



US009246009B2

(12) **United States Patent**
Oikawa et al.

(10) **Patent No.:** **US 9,246,009 B2**
(45) **Date of Patent:** **Jan. 26, 2016**

(54) **SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME**

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(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

(21) Appl. No.: **14/684,774**

(22) Filed: **Apr. 13, 2015**

(65) **Prior Publication Data**

US 2015/0221777 A1 Aug. 6, 2015

Related U.S. Application Data

(62) Division of application No. 12/423,563, filed on Apr. 14, 2009, now Pat. No. 9,006,051.

(30) **Foreign Application Priority Data**

Apr. 18, 2008 (JP) 2008-109119

(51) **Int. Cl.**

H01L 23/31 (2006.01)

H01L 29/06 (2006.01)

(Continued)

(52) **U.S. Cl.**

CPC **H01L 29/78606** (2013.01); **H01L 21/568** (2013.01); **H01L 23/3107** (2013.01); **H01L 23/3114** (2013.01); **H01L 27/1214** (2013.01); **H01L 27/1266** (2013.01);

(Continued)

(58) **Field of Classification Search**

CPC H01L 27/1266; H01L 27/1214; H01L 21/568; H01L 23/3107; H01L 23/3114; H01L 29/06

USPC 438/151, 462; 257/347, 618
See application file for complete search history.

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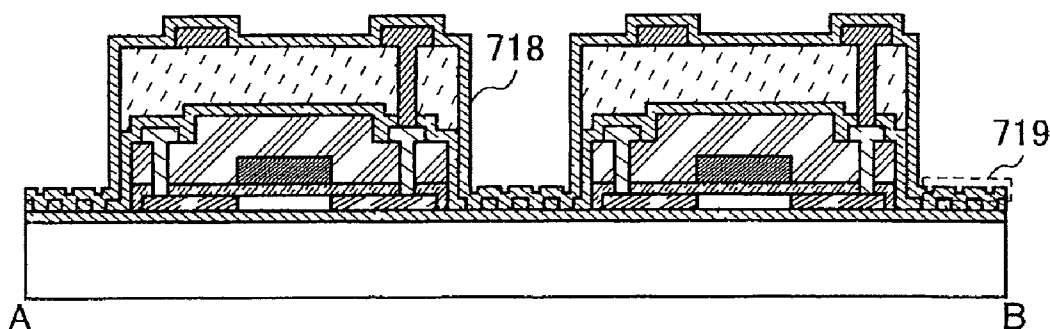
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(57) **ABSTRACT**

An object is to improve water resistance and reliability of a semiconductor device by reducing the degree of peeling of a film. In a semiconductor device, a first inorganic insulating layer, a semiconductor element layer, a second inorganic insulating layer, an organic insulating layer, and a third inorganic insulating layer are sequentially stacked over a substrate. The second inorganic insulating layer is in contact with the first inorganic insulating layer in an opening portion provided in the semiconductor element layer. The third inorganic insulating layer is in contact with the second inorganic insulating layer in an opening portion provided in the organic insulating layer. In a region where the second inorganic insulating layer and the third inorganic insulating layer are in contact with each other, the second inorganic insulating layer has a plurality of irregularities or openings.

17 Claims, 16 Drawing Sheets



- * cited by examiner

FIG. 1A

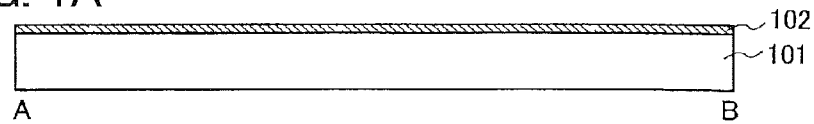


FIG. 1B

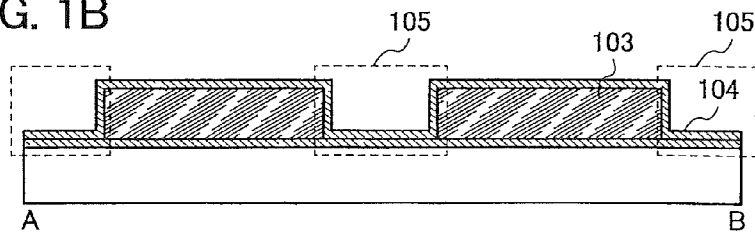


FIG. 1C

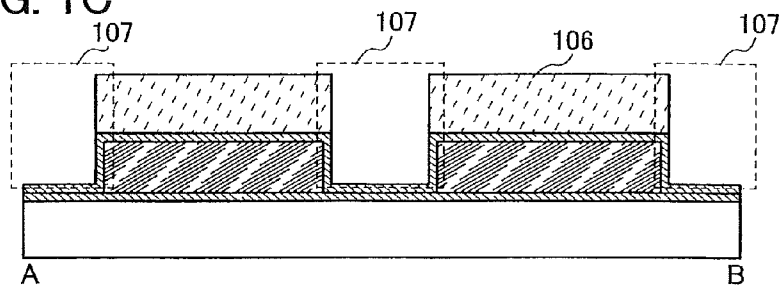


FIG. 1D

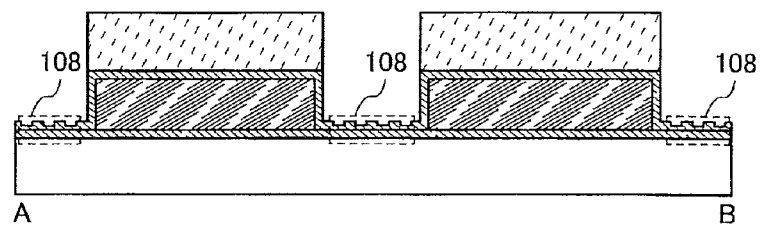


FIG. 1E

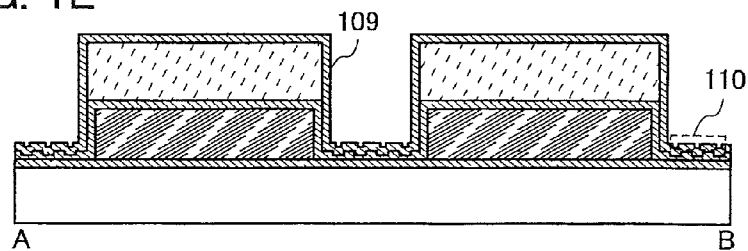


FIG. 2

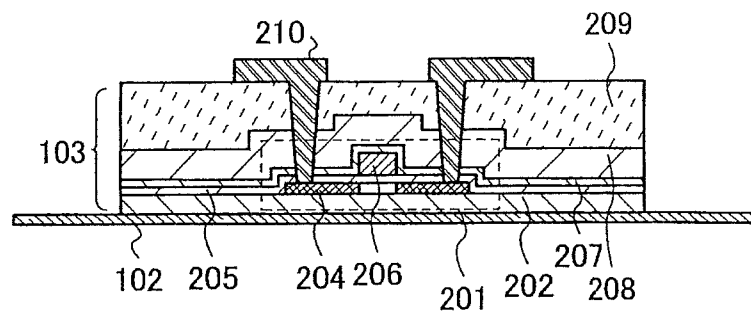


FIG. 3A

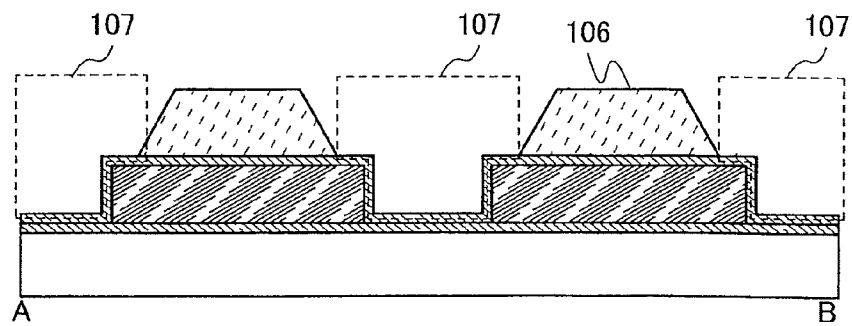


FIG. 3B

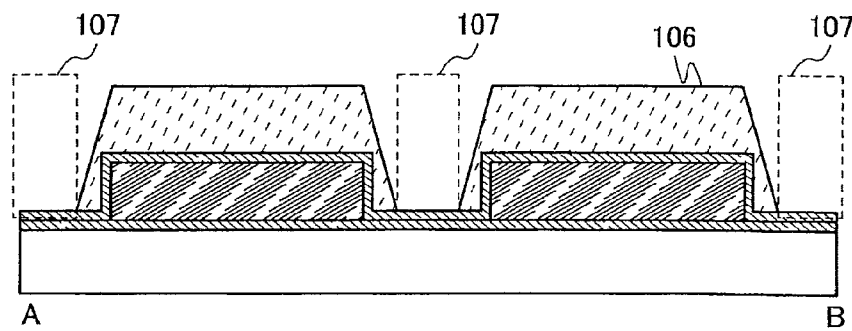


FIG. 4A

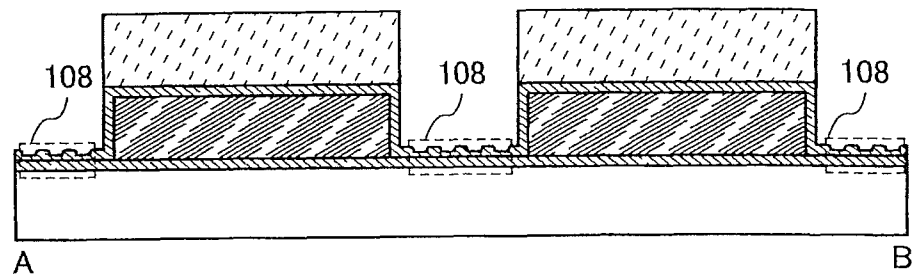


FIG. 4B

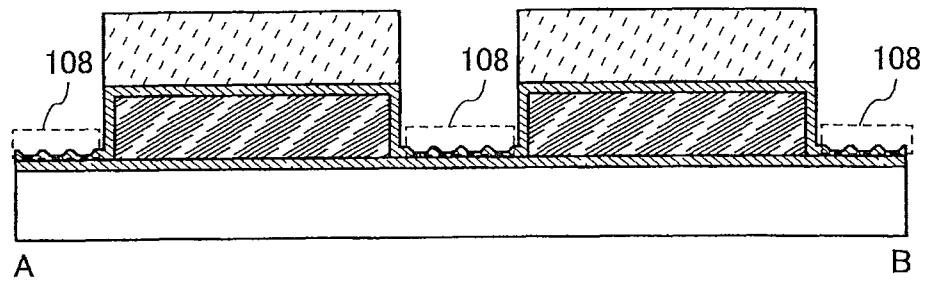


FIG. 5A

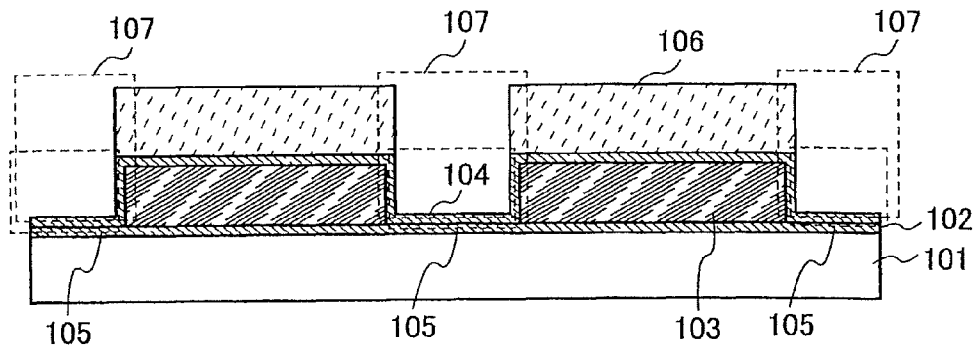


FIG. 5B

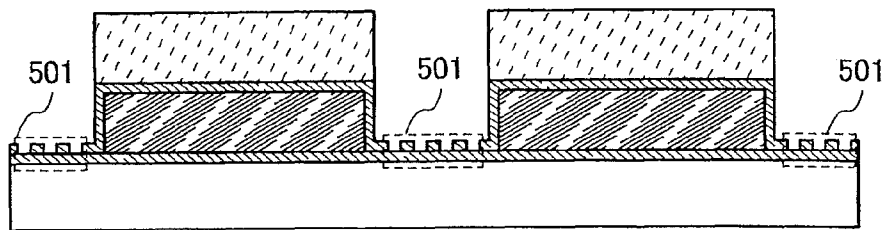


FIG. 5C

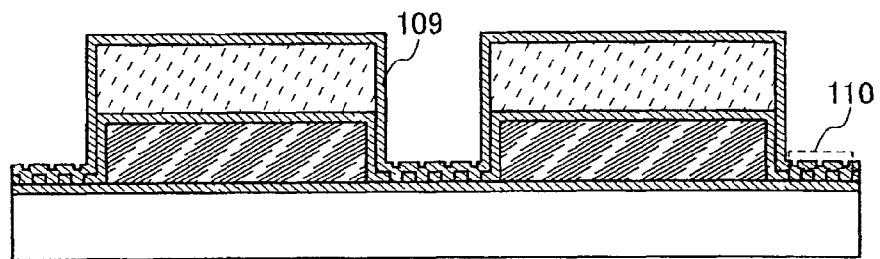


FIG. 6A

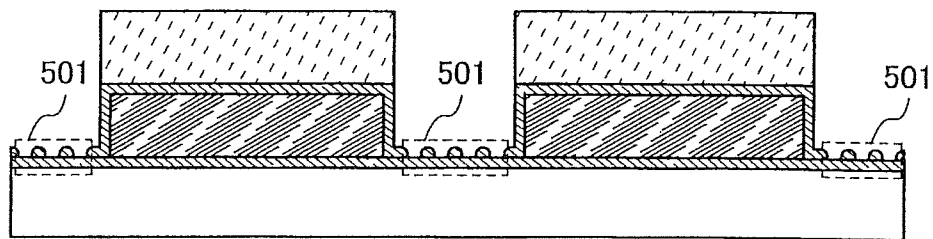


FIG. 6B

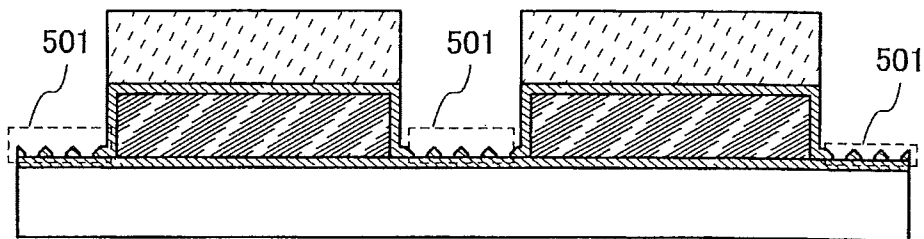


FIG. 7A

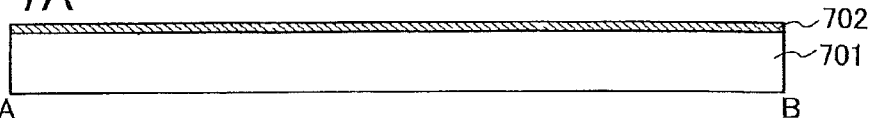


FIG. 7B

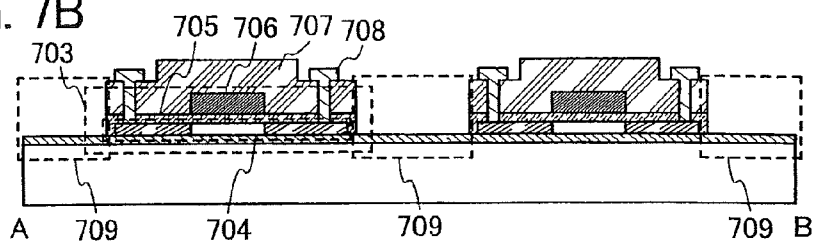


FIG. 7C

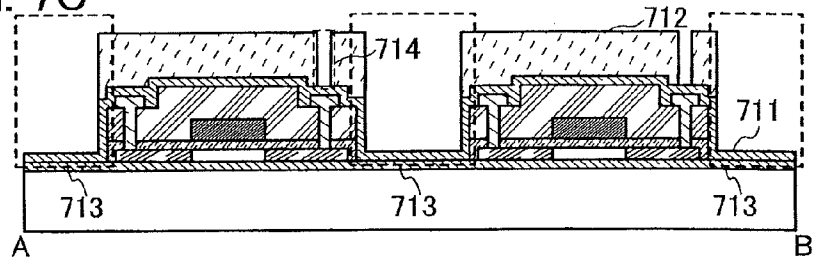


FIG. 7D

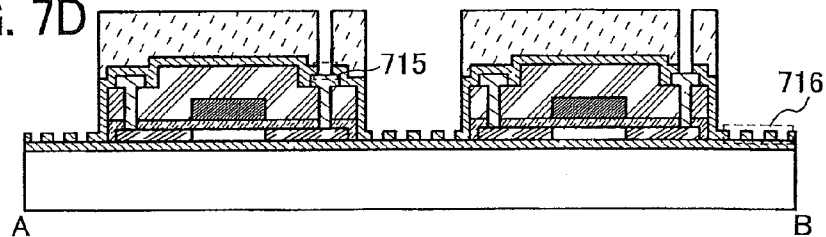


FIG. 7E

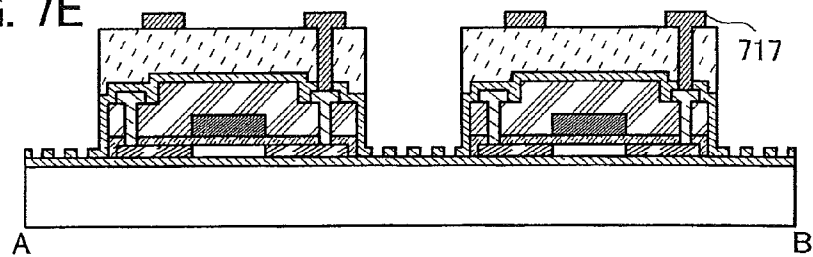


FIG. 7F

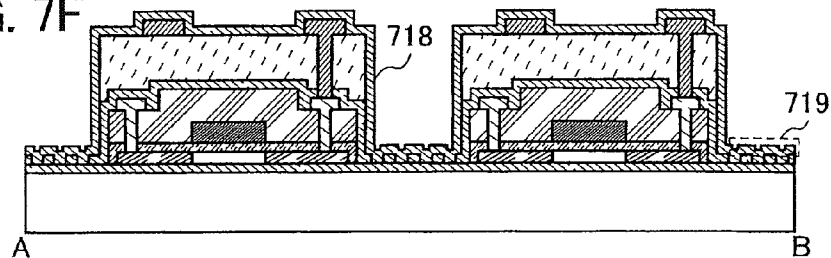


FIG. 8A

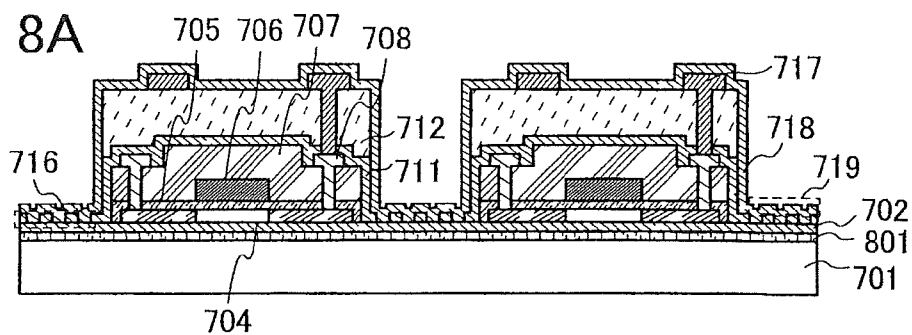


FIG. 8B

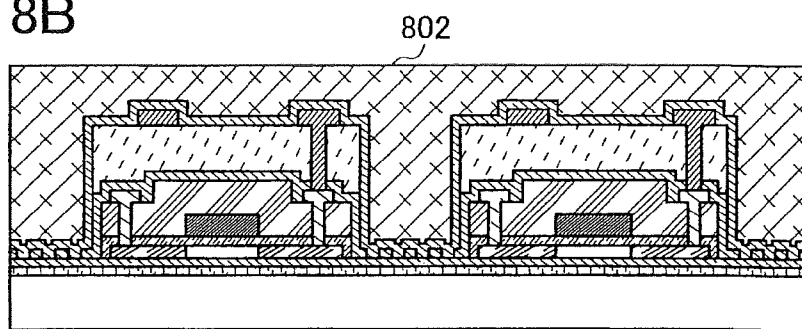


FIG. 8C

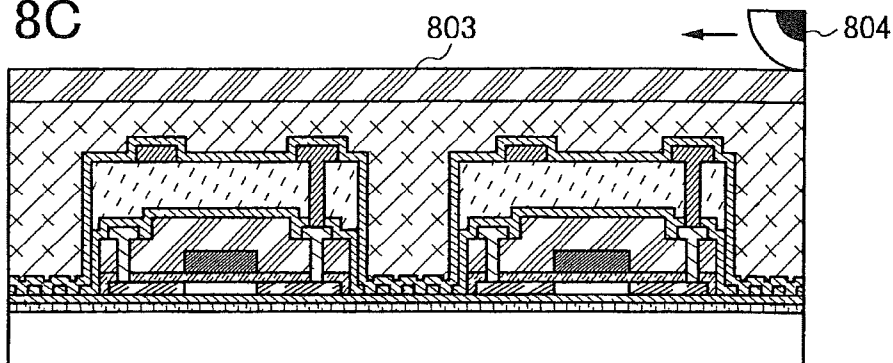


FIG. 8D

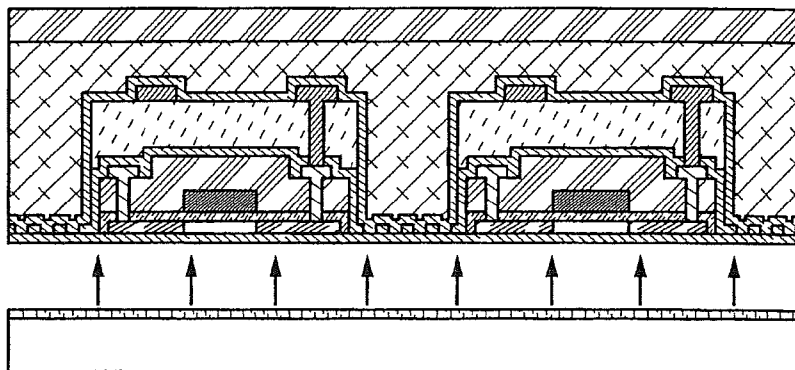


FIG. 9A

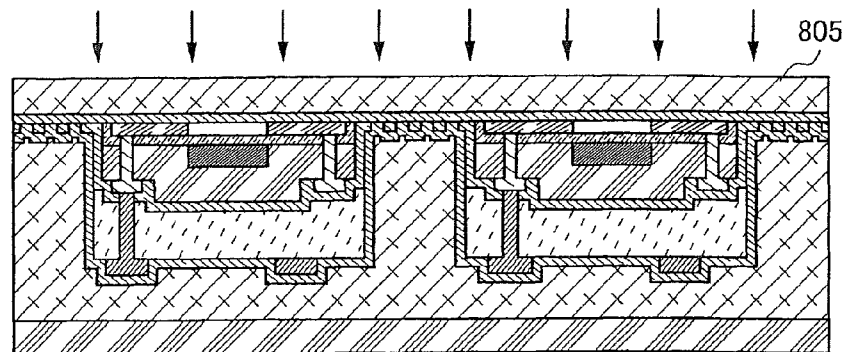


FIG. 9B

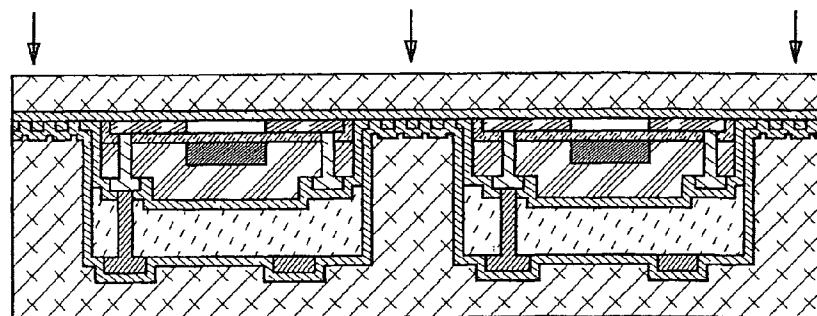


FIG. 9C

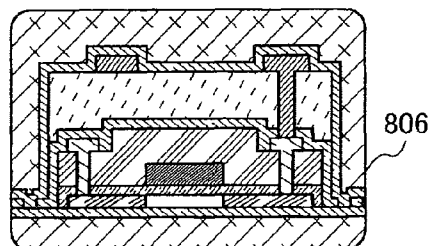


FIG. 10

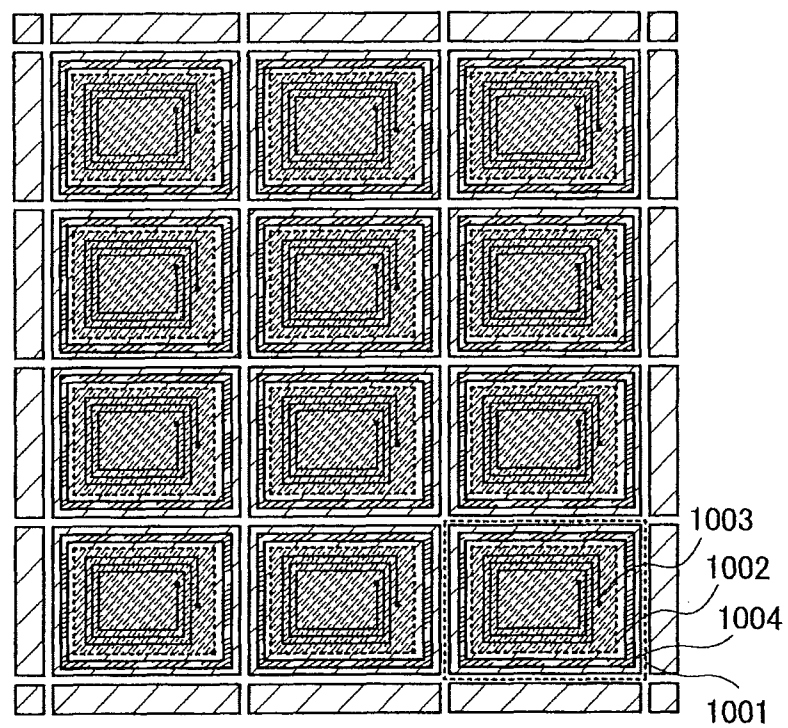


FIG. 11A

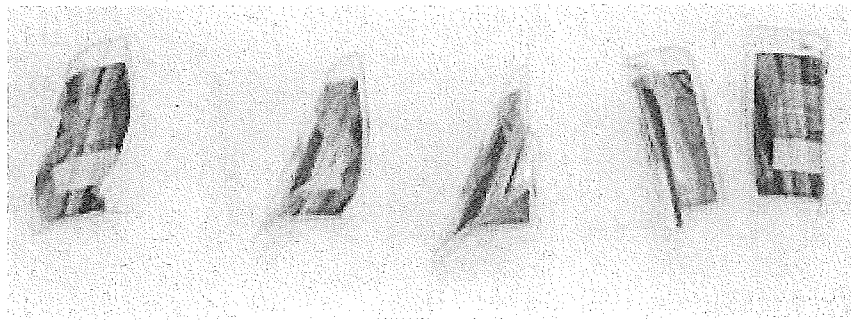


FIG. 11B

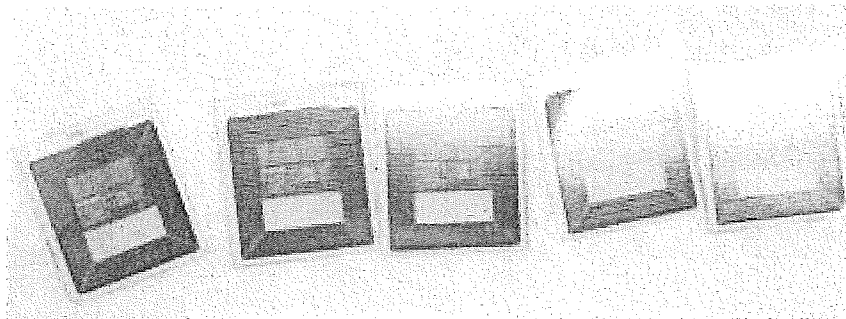


FIG. 12

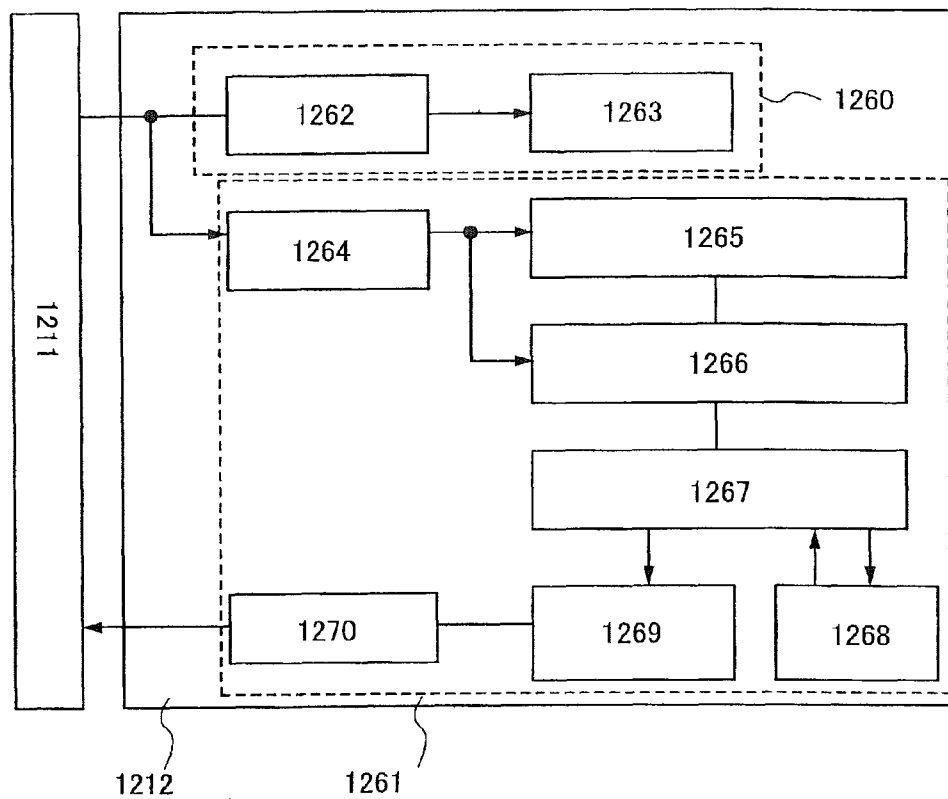


FIG. 13A

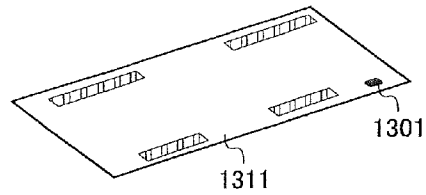


FIG. 13B

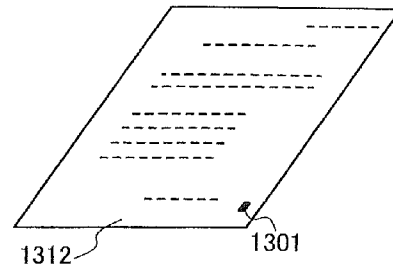


FIG. 13C

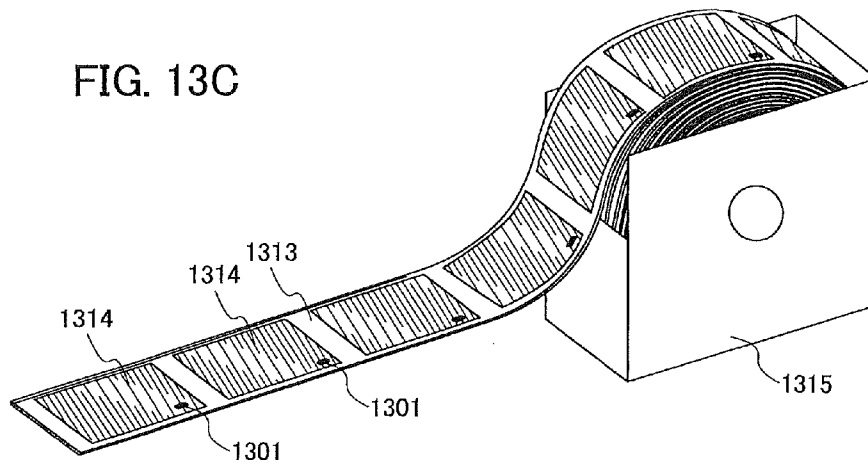


FIG. 13D

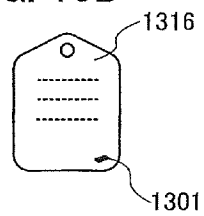


FIG. 13E

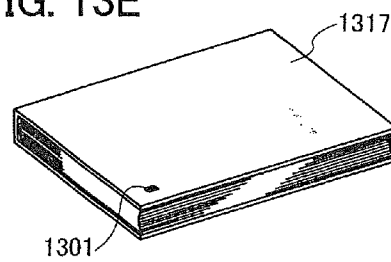


FIG. 14A

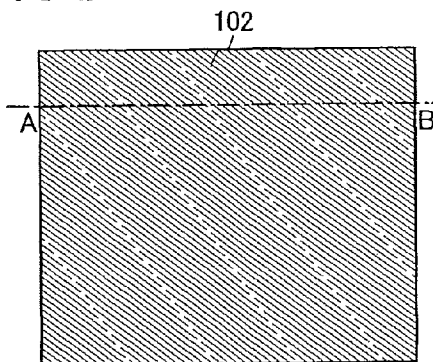


FIG. 14B

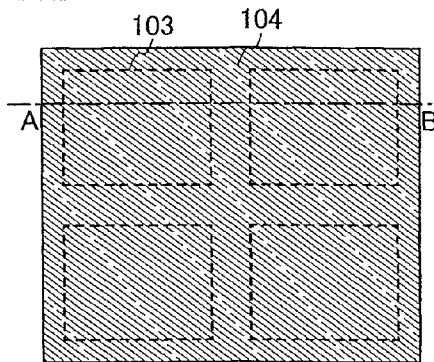


FIG. 14C

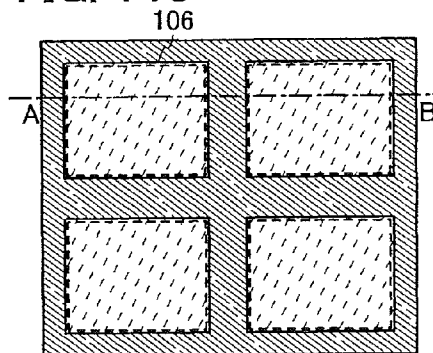


FIG. 14D

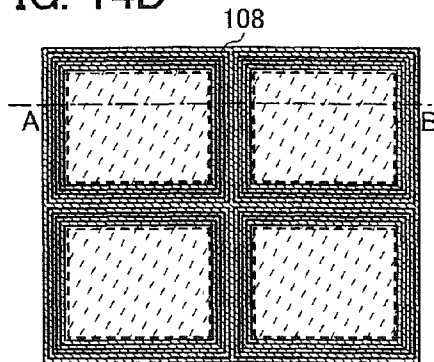


FIG. 14E

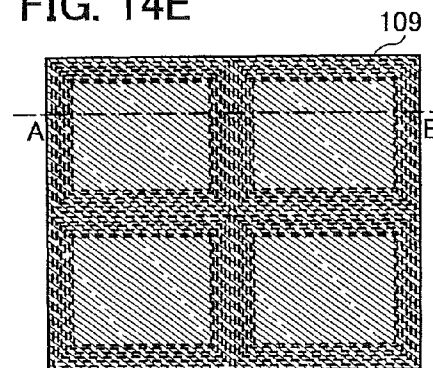


FIG. 14F

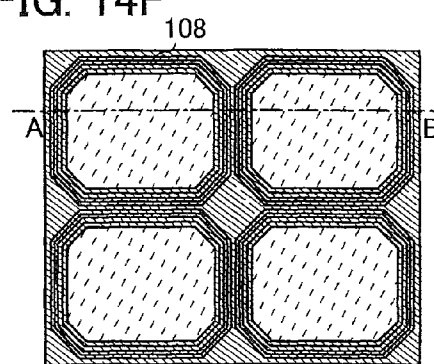


FIG. 15A

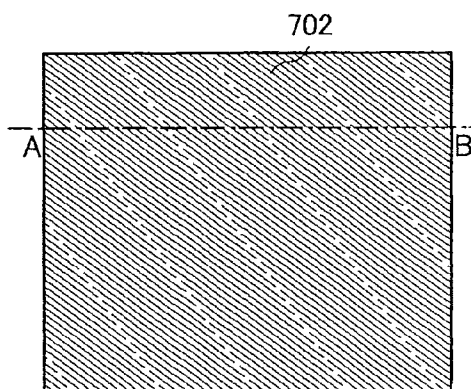


FIG. 15B

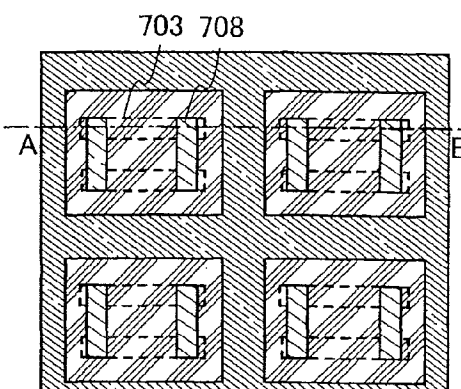


FIG. 15C

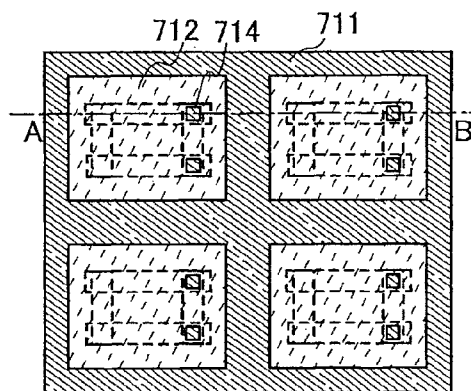


FIG. 15D

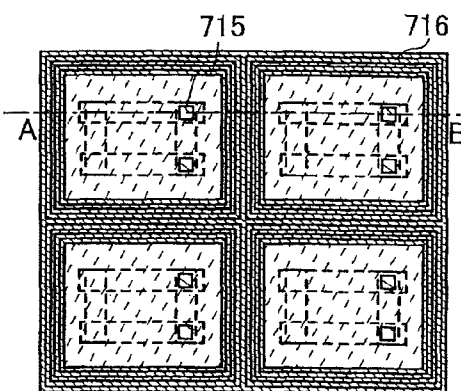


FIG. 15E

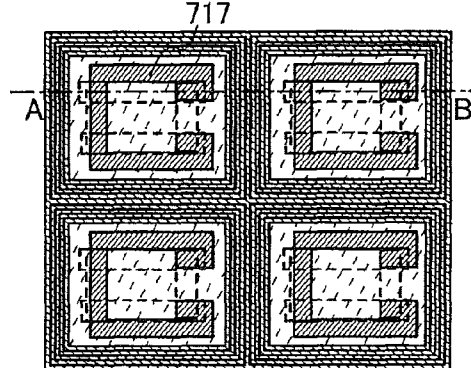


FIG. 15F

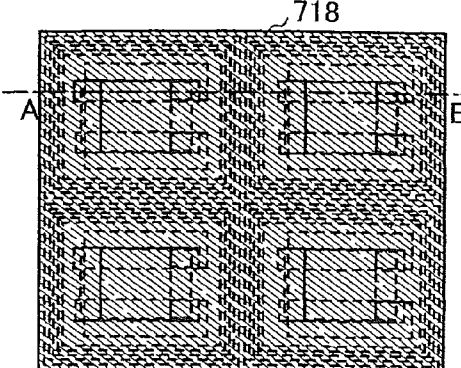
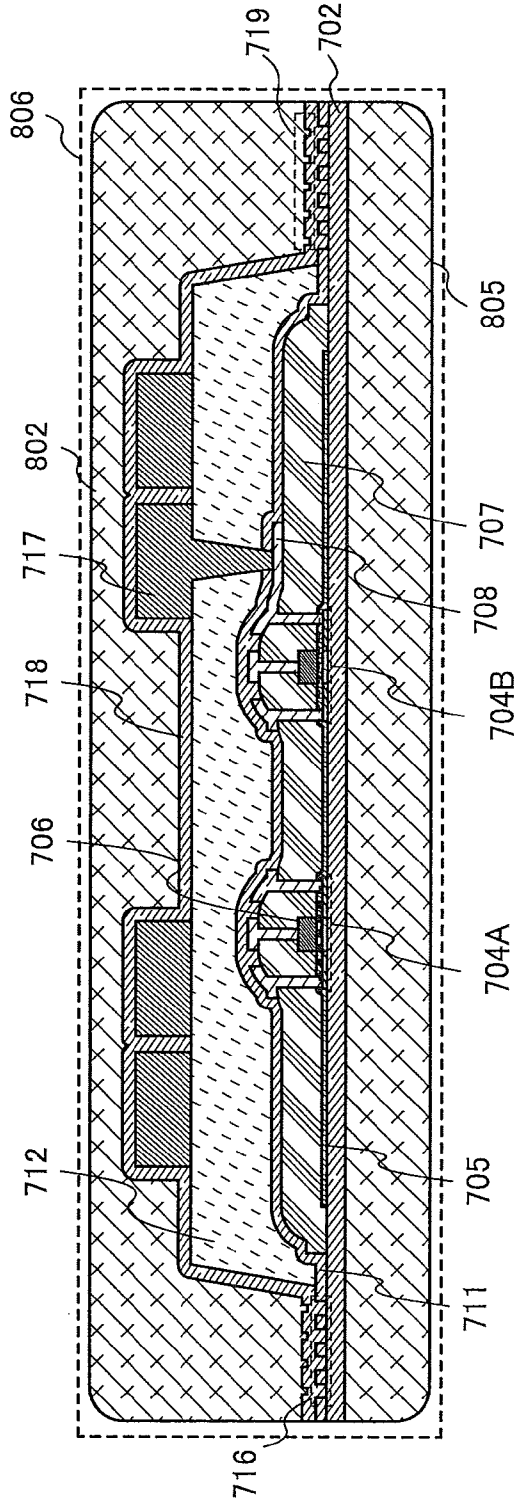


FIG. 16



SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME

This application is a divisional of copending application Ser. No. 12/423,563 filed on Apr. 14, 2009.

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates to semiconductor devices and methods for manufacturing the semiconductor devices.

2. Description of the Related Art

In recent years, an individual identification technology in which an ID (individual identification number) is given to an individual object to clarify information such as a history of the object so that it is used for production, management, and the like has attracted attention. In particular, a semiconductor device that can transmit and receive data without contact (also referred to as an RFID (radio frequency identification) tag, an ID tag, an IC tag, an IC chip, an RF (radio frequency) tag, a wireless tag, an electronic tag, or a wireless chip) has been introduced into companies, markets, and the like. It is important to reduce the thickness of the semiconductor device that can transmit and receive data without contact (hereinafter referred to as a semiconductor device) in order to realize reduction in product size, and a technique for reducing the thickness of the semiconductor device has been developed. A thinned semiconductor device is flexible to some extent and thus can be attached to an object that is bent.

For example, Patent Document 1 (Japanese Published Patent Application No. 2005-311342) discloses a method in which a semiconductor element layer including a thin film transistor formed over a heat-resistant substrate is separated from the substrate and transferred to another substrate, for example, a plastic substrate to manufacture a semiconductor device.

SUMMARY OF THE INVENTION

In a semiconductor element layer including a thin film transistor formed by stacking inorganic insulating layers such as a silicon oxide film and a silicon nitride film, the adhesion between the insulating layers is low, and thus, the film is easily peeled off. Peeling of a film in the semiconductor element layer including the thin film transistor causes degradation of reliability of a semiconductor device due to intrusion of moisture or the like.

For example, when a thin film integrated circuit including a TFT and a flexible substrate which are attached to each other by the above method or the like are cut into a plurality of pieces, a cross section between insulating layers is exposed at a cut surface. When insulating layers exposed at the cut surface are formed using an inorganic insulating layer such as a silicon oxide film or a silicon nitride film, in a preservation test under high temperature and high humidity conditions, intrusion of moisture or the like from the exposed surface occurs, and thus, the flexible substrate is peeled from the base insulating layer. Moreover, when the insulating layers exposed at the cut surface are formed using a silicon oxide film, in the preservation test under high temperature and high humidity conditions, intrusion of moisture or the like from the exposed surface of the silicon oxide film is likely to occur, and thus, a thin film integrated circuit is not normally operated.

One embodiment of the present invention is to provide a semiconductor device with reliability improved by reducing the degree of peeling of a film and a method for manufacturing the semiconductor device. Another embodiment of the

present invention is to provide a semiconductor device with reliability improved by reducing the degree of peeling of a film in a preservation test under high temperature and high humidity conditions, and a method for manufacturing the semiconductor device.

Features of the present invention in a semiconductor device formed by sequentially stacking a first inorganic insulating layer, a semiconductor element layer including a thin film transistor, a second inorganic insulating layer, an organic insulating layer, and a third inorganic insulating layer over a substrate are as follows. The second inorganic insulating layer is in contact with the first inorganic insulating layer in an opening portion provided in the semiconductor element layer. The third inorganic insulating layer is in contact with the second inorganic insulating layer in an opening portion provided in the organic insulating layer. In a region where the second inorganic insulating layer and the third inorganic insulating layer are in contact with each other, a surface of the second inorganic insulating layer has a plurality of irregularities or a plurality of opening portions.

One embodiment of the present invention is a semiconductor device described as follows. A first inorganic insulating layer, a semiconductor element layer, a second inorganic insulating layer, an organic insulating layer, and a third inorganic insulating layer are sequentially stacked over a substrate. The second inorganic insulating layer is in contact with the first inorganic insulating layer in an opening portion provided in the semiconductor element layer. The third inorganic insulating layer is in contact with the second inorganic insulating layer in an opening portion provided in the organic insulating layer. In a region where the second inorganic insulating layer and the third inorganic insulating layer are in contact with each other, a surface of the second inorganic insulating layer has a plurality of irregularities.

Another embodiment of the present invention is a semiconductor device described as follows. A first inorganic insulating layer, a semiconductor element layer, a second inorganic insulating layer, an organic insulating layer, and a third inorganic insulating layer are sequentially stacked over a substrate. The second inorganic insulating layer is in contact with the first inorganic insulating layer in an opening portion provided in the semiconductor element layer. The third inorganic insulating layer is in contact with the second inorganic insulating layer in an opening portion provided in the organic insulating layer. In a region where the second inorganic insulating layer and the third inorganic insulating layer are in contact with each other, a surface of the second inorganic insulating layer has a plurality of irregularities. In a region where the third inorganic insulating layer overlaps with the plurality of irregularities of the second inorganic insulating layer, a surface of the third inorganic insulating layer has a plurality of irregularities.

Another embodiment of the present invention is a semiconductor device described as follows. A first inorganic insulating layer, a semiconductor element layer, a second inorganic insulating layer, an organic insulating layer, and a third inorganic insulating layer are sequentially stacked over a substrate. The second inorganic insulating layer is in contact with the first inorganic insulating layer in an opening portion provided in the semiconductor element layer. The third inorganic insulating layer is in contact with the second inorganic insulating layer in an opening portion provided in the organic insulating layer. In a region where the second inorganic insulating layer and the third inorganic insulating layer are in contact with each other, a plurality of opening portions are formed in the second inorganic insulating layer. The first

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inorganic insulating layer and the third inorganic insulating layer are in contact with each other in the plurality of opening portions.

Still another embodiment of the present invention is a semiconductor device described as follows. A first inorganic insulating layer, a semiconductor element layer, a second inorganic insulating layer, an organic insulating layer, and a third inorganic insulating layer are sequentially stacked over a substrate. The second inorganic insulating layer is in contact with the first inorganic insulating layer in an opening portion provided in the semiconductor element layer. The third inorganic insulating layer is in contact with the second inorganic insulating layer in an opening portion provided in the organic insulating layer. In a region where the second inorganic insulating layer and the third inorganic insulating layer are in contact with each other, a plurality of opening portions are formed in the second inorganic insulating layer. The first inorganic insulating layer and the third inorganic insulating layer are in contact with each other in the plurality of opening portions. In a region where the third inorganic insulating layer overlaps with the plurality of opening portions provided in the second inorganic insulating layer, a surface of the third inorganic insulating layer has a plurality of irregularities.

Another embodiment of the present invention is a semiconductor device described as follows. A first inorganic insulating layer, a semiconductor element layer, a second inorganic insulating layer, an organic insulating layer, a conductive layer, and a third inorganic insulating layer are sequentially stacked over a substrate. The second inorganic insulating layer is in contact with the first inorganic insulating layer in an opening portion provided in the semiconductor element layer. The third inorganic insulating layer is in contact with the second inorganic insulating layer in an opening portion provided in the organic insulating layer. The conductive layer is electrically connected to the semiconductor element layer in an opening portion provided in the organic insulating layer and the second inorganic insulating layer. In a region where the second inorganic insulating layer and the third inorganic insulating layer are in contact with each other, a plurality of opening portions are formed in the second inorganic insulating layer.

A further embodiment of the present invention is a semiconductor device described as follows. A first inorganic insulating layer, a semiconductor element layer, a second inorganic insulating layer, an organic insulating layer, a conductive layer, and a third inorganic insulating layer are sequentially stacked over a substrate. The second inorganic insulating layer is in contact with the first inorganic insulating layer in an opening portion provided in the semiconductor element layer. The third inorganic insulating layer is in contact with the second inorganic insulating layer in an opening portion provided in the organic insulating layer. The conductive layer is electrically connected to the semiconductor element layer in an opening portion provided in the organic insulating layer and the second inorganic insulating layer. In a region where the second inorganic insulating layer and the third inorganic insulating layer are in contact with each other, a plurality of opening portions are formed in the second inorganic insulating layer. The first inorganic insulating layer and the third inorganic insulating layer are in contact with each other in the plurality of opening portions.

In addition, one embodiment of the present invention is a method for manufacturing a semiconductor device, including the steps of: forming a separation layer over a substrate; forming a first inorganic insulating layer over the separation layer; forming a semiconductor element layer over the first inorganic insulating layer; forming an opening portion in the

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semiconductor element layer; forming a second inorganic insulating layer over the semiconductor element layer and a surface of the first inorganic insulating layer, which is exposed by the opening portion provided in the semiconductor element layer; forming an organic insulating layer over the semiconductor element layer with the second inorganic insulating layer interposed therebetween; forming an opening portion in the organic insulating layer; forming a plurality of opening portions in parts of the second inorganic insulating layer, which are exposed by the opening portion provided in the semiconductor element layer and the opening portion provided in the organic insulating layer; and forming a third inorganic insulating layer over the plurality of opening portions and the organic insulating layer.

Another embodiment of the present invention is a method for manufacturing a semiconductor device, including the steps of: forming a separation layer over a substrate; forming a first inorganic insulating layer over the separation layer; forming a semiconductor element layer over the first inorganic insulating layer; forming an opening portion in the semiconductor element layer; forming a second inorganic insulating layer over the semiconductor element layer and a surface of the first inorganic insulating layer, which is exposed by the opening portion provided in the semiconductor element layer; forming an organic insulating layer over the semiconductor element layer with the second inorganic insulating layer interposed therebetween; forming an opening portion in the organic insulating layer; forming a plurality of opening portions in parts of the second inorganic insulating layer, which are exposed by the opening portion provided in the semiconductor element layer and the opening portion provided in the organic insulating layer; forming a conductive layer over the organic insulating layer and the plurality of opening portions provided over the semiconductor element layer; and forming a third inorganic insulating layer over the plurality of opening portions, the conductive layer, and the organic insulating layer.

Still another embodiment of the present invention is a method for manufacturing a semiconductor device, including the steps of: forming a separation layer over a substrate; forming a first inorganic insulating layer over the separation layer; forming a semiconductor element layer over the first inorganic insulating layer; forming an opening portion in the semiconductor element layer; forming a second inorganic insulating layer over the semiconductor element layer and a surface of the first inorganic insulating layer, which is exposed by the opening portion provided in the semiconductor element layer; forming an organic insulating layer over the semiconductor element layer with the second inorganic insulating layer interposed therebetween; thinning an opening portion in the organic insulating layer; forming a plurality of opening portions in parts of the second inorganic insulating layer, which are exposed by the opening portion provided in the semiconductor element layer and the opening portion provided in the organic insulating layer; forming a first sealing layer including a fibrous body and an organic resin layer, over the third inorganic insulating layer; physically separating the substrate and the separation layer; forming a second sealing layer on a surface of the first inorganic insulating layer, which is exposed by separating the separation layer; and cutting a region where the plurality of opening portions formed in the second inorganic insulating layer are provided.

A further embodiment of the present invention is a method for manufacturing a semiconductor device, including the steps of: forming a separation layer over a substrate; forming a first inorganic insulating layer over the separation layer; forming a semiconductor element layer over the first inorganic

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ganic insulating layer; forming an opening portion in the semiconductor element layer; forming a second inorganic insulating layer over the semiconductor element layer and a surface of the first inorganic insulating layer, which is exposed by the opening portion provided in the semiconductor element layer; forming an organic insulating layer over the semiconductor element layer with the second inorganic insulating layer interposed therebetween; forming an opening portion in the organic insulating layer; forming a plurality of opening portions in parts of the second inorganic insulating layer, which are exposed by the opening portion provided in the semiconductor element layer and the opening portion provided in the organic insulating layer; forming a conductive layer over the organic insulating layer and the plurality of opening portions provided over the semiconductor element layer; forming a third inorganic insulating layer over the plurality of opening portions, the conductive layer, and the organic insulating layer; forming a first sealing layer including a fibrous body and an organic resin layer, over the third inorganic insulating layer; physically separating the substrate and the separation layer; forming a second sealing layer on a surface of the first inorganic insulating layer, which is exposed by separating the separation layer; and cutting a region where the plurality of opening portions formed in the second inorganic insulating layer are provided.

In the semiconductor device formed according to one embodiment of the present invention, the adhesion between the second inorganic insulating layer and the third inorganic insulating layer can be particularly increased, and the degree of peeling of a film from an edge portion can be reduced especially in the preservation test under high temperature and high humidity conditions. Accordingly, intrusion of moisture into the semiconductor element layer from an interface between the second inorganic insulating layer and the third inorganic insulating layer can be suppressed. That is, heat resistance and moisture resistance can be improved, and a semiconductor device with improved reliability and a method for manufacturing the semiconductor device can be provided.

BRIEF DESCRIPTION OF THE DRAWINGS

In the accompanying drawings:

FIGS. 1A to 1E are cross-sectional views illustrating semiconductor devices;

FIG. 2 is a cross-sectional view illustrating a semiconductor device;

FIGS. 3A and 3B are cross-sectional views illustrating semiconductor devices;

FIGS. 4A and 4B are cross-sectional views illustrating semiconductor devices;

FIGS. 5A to 5C are cross-sectional views illustrating semiconductor devices;

FIGS. 6A and 6B are cross-sectional views illustrating semiconductor devices;

FIGS. 7A to 7F are cross-sectional views illustrating semiconductor devices;

FIGS. 8A to 8D are cross-sectional views illustrating the semiconductor devices;

FIGS. 9A to 9C are cross-sectional views illustrating the semiconductor devices;

FIG. 10 is a top view illustrating semiconductor devices;

FIGS. 11A and 11B are photographs for illustrating effect of irregularities in semiconductor devices;

FIG. 12 is a block diagram illustrating a semiconductor device;

FIGS. 13A to 13E illustrate semiconductor devices;

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FIGS. 14A to 14F are top views illustrating the semiconductor devices;

FIGS. 15A to 15F are top views illustrating the semiconductor devices; and

FIG. 16 is a cross-sectional view illustrating a semiconductor device.

DETAILED DESCRIPTION OF THE INVENTION

Hereinafter, embodiments of the present invention will be described with reference to the accompanying drawings. Note that the present invention can be implemented in various modes, and it is easily understood by those skilled in the art that modes and details can be variously changed without departing from the spirit and scope of the present invention. Therefore, the present invention is not construed as being limited to what is described in the embodiments. Note that in the drawings, the same portions or portions having similar functions are denoted by the same reference numerals, and the description will not be repeated.

Embodiment 1

This embodiment will be described with reference to FIGS. 1A to 1E, FIG. 2, FIGS. 3A and 3B, FIGS. 4A and 4B, and FIGS. 14A to 14F. Note that FIGS. 14A to 14E are top views corresponding to the cross-sectional views of FIGS. 1A to 1E.

First, a first inorganic insulating layer **102** is formed over a substrate **101** (see FIG. 1A and FIG. 14A).

As the substrate **101**, a glass substrate, a quartz substrate, a ceramic substrate, a metal substrate in which an insulating layer is formed on at least one surface, an organic resin substrate, or the like can be used. As an example, a glass substrate is used as the substrate **101**.

The first inorganic insulating layer **102** is formed using a single layer or a stack of an inorganic compound by a sputtering method, a plasma CVD method, a coating method, a printing method, or the like. The inorganic compound used for the first inorganic insulating layer **102** having a single-layer structure is silicon nitride (SiNx) or silicon nitride oxide (SiNxOy) ($x > y$). Alternatively, the first inorganic insulating layer **102** may have a stacked structure. The inorganic compounds used for the first inorganic insulating layer having a stacked structure are silicon oxide (SiOx), silicon nitride (SiNx), silicon oxynitride (SiOxNy) ($x > y$), and/or silicon nitride oxide (SiNxOy) ($x > y$). When the first inorganic insulating layer **102** has a two-layer structure, it is preferable that, for example, a silicon oxynitride film be a first layer (a layer that is in contact with the substrate **101**) and a silicon nitride film be a second layer. When the insulating layer serving as a base has a three-layer structure, it is preferable that a first insulating film (a layer that is in contact with the substrate **101**) be a silicon oxide film, a second insulating film be a silicon oxynitride film, and a third insulating film be a silicon nitride film. The first inorganic insulating layer **102** which includes a layer containing silicon nitride or silicon nitride oxide functions as a blocking film for preventing impurities and moisture from entering a semiconductor element layer **103** to be formed over the first inorganic insulating layer **102**.

Note that silicon oxynitride contains more oxygen than nitrogen and, in the case where measurements are performed using Rutherford backscattering spectrometry (RBS) and hydrogen forward scattering (HFS), includes oxygen, nitrogen, silicon, and hydrogen at concentrations ranging from 50 at. % to 70 at. %, 0.5 at. % to 15 at. %, 25 at. % to 35 at. %, and 0.1 at. % to 10 at. %, respectively. In addition, silicon nitride oxide contains more nitrogen than oxygen and, in the case

where measurements are performed using RBS and HFS, includes oxygen, nitrogen, silicon, and hydrogen at concentrations ranging from 5 at. % to 30 at. %, 20 at. % to 55 at. %, 25 at. % to 35 at. %, and 10 at. % to 25 at. %, respectively. Note that percentages of nitrogen, oxygen, silicon, and hydrogen fall within the ranges given above, where the total number of atoms contained in the silicon oxynitride or the silicon nitride oxide is defined as 100 at. %.

Note that terms such as first, second, third to N-th (N is a natural number) used in this specification are given in order to avoid confusion between components and do not limit the number of components.

Next, the semiconductor element layer **103** is formed over the first inorganic insulating layer **102**, and a second inorganic insulating layer **104** is formed so as to cover the semiconductor element layer **103** (see FIG. 1B and FIG. 14B). Although not shown, description in this embodiment is made on the assumption that the semiconductor element layers **103** are provided over the first inorganic insulating layer **102** in accordance with the respective regions functioning as a semiconductor device and then cut to obtain a plurality of semiconductor devices. Note that even when one semiconductor element layer **103** is formed over the first inorganic insulating layer, the structure shown in this embodiment can reduce the degree of peeling of a film at an edge portion particularly in a preservation test under high temperature and high humidity conditions, and can improve reliability.

As an example of the semiconductor element layer **103**, FIG. 2 illustrates the semiconductor element layer **103** including a thin film transistor **201** over the first inorganic insulating layer **102**. Note that although not shown in FIG. 2, the semiconductor element layer **103** over the first inorganic insulating layer **102** includes a plurality of thin film transistors.

The thin film transistor **201** formed over a base film **202** includes a semiconductor layer **204** having a source region, a drain region, and a channel formation region; a gate insulating layer **205**; and a gate electrode **206**.

Note that the base film **202** and a film in the first semiconductor element layer **102**, which is on the side not in contact with the glass substrate, function as a blocking film for preventing impurities from entering the semiconductor layer **204** in the semiconductor element layer and as a film for increasing the adhesion between the first inorganic insulating layer **102** and the semiconductor layer **204**. As the base film **202**, a single layer or a stack of a silicon oxide film, a silicon nitride oxide film, a silicon nitride film, or a silicon oxynitride film can be used. Note that the base film **202** can be omitted when the first inorganic insulating layer can also function as the base film **202**. Further, the gate electrode **206** provided over the semiconductor layer **204** with the gate insulating layer interposed therebetween may be formed using a single layer or a stack of a conductive film such as a metal film. In this embodiment, the gate electrode **206** can be formed using a stack of a tantalum nitride film and a tungsten film, for example.

An interlayer insulating film **207**, an interlayer insulating film **208**, and an interlayer insulating film **209** are formed to cover the thin film transistor **201**. Moreover, wirings **210** that are in contact with the source region and the drain region in the semiconductor layer **204** are formed over the interlayer insulating film **209**. Note that as the gate insulating layer **205** and the interlayer insulating films **207**, **208**, and **209**, any of a silicon oxide film, a silicon nitride oxide film, a silicon nitride film, or a silicon oxynitride film may be used. In this embodiment, a silicon oxynitride film is formed as the gate insulating layer **205** and the interlayer insulating films **207** and **209**, and

a silicon nitride oxide film is formed as the interlayer insulating film **208**. Further, the wirings **210** formed over the interlayer insulating film **209** may be formed using a single layer or a stack of a conductive film such as a metal film. In this embodiment, the wirings **210** are formed using a stack of three layers of a titanium film, an aluminum film, and a titanium film, for example.

Note that the semiconductor element layer **103** refers to not only a layer including a thin film transistor as illustrated in FIG. 2, but also a layer including a plurality of elements formed using semiconductor characteristics. For example, the semiconductor element layer **103** may include a plurality of elements such as a diode, a resistor, a capacitor, or a memory element in addition to a thin film transistor.

Referring back to FIG. 1B, in the semiconductor element layer **103** in which the formation of the wirings **210** illustrated in FIG. 2 is completed, the base film **202**, the gate insulating layer **205**, and the interlayer insulating films **207**, **208**, and **209** are etched, so that opening portions **105** are formed between the semiconductor element layers **103** as illustrated in FIG. 1B. The second inorganic insulating layer **104** formed so as to cover the semiconductor element layer **103** is provided to be in contact with the first inorganic insulating layer **102** in the opening portion **105**. In this embodiment, the semiconductor element layer **103** can be surrounded by the first inorganic insulating layer **102** and the second inorganic insulating layer **104** each containing silicon nitride or silicon nitride oxide, whereby intrusion of impurities and moisture can further be suppressed, and a semiconductor device with higher reliability can be obtained.

The second inorganic insulating layer **104** is formed using a single layer or a stack of an inorganic compound by a sputtering method, a plasma CVD method, a coating method, a printing method, or the like. The inorganic compound used for the second inorganic insulating layer **104** having a single-layer structure is silicon nitride (SiN_x) or silicon nitride oxide (SiN_xO_y) ($x > y$). Alternatively, the second inorganic insulating layer **104** may have a stacked structure. The inorganic compounds used for the second inorganic insulating layer **104** having a stacked structure are silicon oxide (SiO_x), silicon nitride (SiN_x), silicon oxynitride (SiO_xN_y) ($x > y$), and/or silicon nitride oxide (SiN_xO_y) ($x > y$). The second inorganic insulating layer **104** which contains silicon nitride or silicon nitride oxide functions as a blocking film for preventing impurities and moisture from entering the semiconductor element layer **103** formed below the second inorganic insulating layer **104**.

Next, an organic insulating layer **106** is formed over the second inorganic insulating layer **104**. Then, etching is performed so that the organic insulating layer **106** remains over the semiconductor element layer **103** with the second inorganic insulating layer **104** interposed therebetween, whereby opening portions **107** are formed (see FIG. 1C and FIG. 14C). Note that FIG. 1C illustrates the structure in which the organic insulating layer **106** is provided over the semiconductor element layer **103** and over the second inorganic insulating layer **104** except in a region where the first inorganic insulating layer **102** and the second inorganic insulating layer **104** are in direct contact with each other. However, there is no particular limitation on the structure, and another structure may be employed. For example, as illustrated in FIG. 3A, the area of the opening portion **107** in the organic insulating layer **106** may be larger than that of the region where the first inorganic insulating layer **102** and the second inorganic insulating layer **104** are in direct contact with each other. Alternatively, as illustrated in FIG. 3B, the area of the opening portion **107** in the organic insulating layer **106** may be smaller than that of

the region where the first inorganic insulating layer **102** and the second inorganic insulating layer **104** are in direct contact with each other. Note that as illustrated in FIGS. **3A** and **3B**, the cross-sectional shape of edge portions of the organic insulating layer is preferably tapered when the organic insulating layer is processed by etching. The tapered shape of the edge portions can prevent disconnection of the wiring due to the step shape. In the structure shown in this embodiment, the semiconductor element layer **103** is surrounded by the first inorganic insulating layer **102** and the second inorganic insulating layer **104** which contain silicon nitride or silicon nitride oxide, whereby intrusion of impurities or moisture from the organic insulating layer into the semiconductor element layer **103** can be prevented even in the structures illustrated in FIGS. **3A** and **3B**. Note that in this embodiment, description is made on the assumption that the opening portion **107** is formed while the organic insulating layer **106** remains over the semiconductor element layer **103** with the second inorganic insulating layer **104** interposed therebetween.

Then, in the region where the first inorganic insulating layer **102** and the second inorganic insulating layer **104** are in direct contact with each other, a surface of the second inorganic insulating layer **104** is processed to have a plurality of irregularities **108** (see FIG. **1D** and FIG. **14D**). The plurality of irregularities **108** may be formed through steps such as resist application using a photosensitive resin called a photoresist, pattern exposure, development, selective etching by anisotropic etching using the resist as a mask, and resist removal by using a lithography technique. Note that as illustrated in FIG. **1D**, a surface of the plurality of irregularities **108** may have a cross-sectional shape such that upper portions of the projections are columnar. Alternatively, the upper portions of the plurality of irregularities **108** may be rounded as illustrated in FIG. **4A**, or may be substantially pointed as illustrated in FIG. **4B**. Note that in the top view of FIG. **14D**, a region where the plurality of irregularities **108** are provided is rectangular corresponding to the shape of the region where the semiconductor element layer **103** is provided; however, the shape of the region is not particularly limited thereto. For example, with a structure illustrated in FIG. **14F**, in which the region occupied by the semiconductor element layer **103** has a shape with chamfered corners and the plurality of irregularities **108** are provided so as to surround the region, the degree of peeling of a film can be reduced especially in the preservation test under high temperature and high humidity conditions.

Next, a third inorganic insulating layer **109** is formed to cover the organic insulating layer **106** and the second inorganic insulating layer **104** provided with the plurality of irregularities **108** (see FIG. **1E** and FIG. **14E**). The third inorganic insulating layer **109** can suppress intrusion of moisture and impurities into the semiconductor element layer. Further, when the second inorganic insulating layer **104** has the plurality of irregularities **108**, the area where the second inorganic insulating layer **104** and the third inorganic insulating layer **109** are in direct contact with each other can be increased. Accordingly, the adhesion between the second inorganic insulating layer **104** and the third inorganic insulating layer **109** can be increased.

The third inorganic insulating layer **109** is formed using a single layer or a stack of an inorganic compound by a sputtering method, a plasma CVD method, a coating method, a printing method, or the like. The inorganic compound used for the third inorganic insulating layer **109** having a single-layer structure is silicon nitride (SiN_x) or silicon nitride oxide (SiN_xO_y) ($x>y$). Alternatively, the third inorganic insulating layer **109** may have a stacked structure. The inorganic com-

pounds used for the third inorganic insulating layer **109** having a stacked structure are silicon oxide (SiO_x), silicon nitride (SiN_x), silicon oxynitride (SiO_xN_y) ($x>y$), and/or silicon nitride oxide (SiN_xO_y) ($x>y$). The third inorganic insulating layer **109** which contains silicon nitride or silicon nitride oxide functions as a blocking film for preventing impurities and moisture from entering the semiconductor element layer **103** surrounded by the first inorganic insulating layer **102** and the second inorganic insulating layer **104**.

Moreover, in a region where the third inorganic insulating layer **109** overlaps with the plurality of irregularities **108** of the second inorganic insulating layer **104**, a surface of the third inorganic insulating layer **109** has a plurality of irregularities **110**. Note that as illustrated in FIG. **1E**, the size or depth of the recessed portion in a cross section of the plurality of irregularities **110** of the surface of the third inorganic insulating layer **109** varies depending on the size or depth of the recessed portion of the plurality of irregularities **108** of the second inorganic insulating layer **104** or the thickness or step coverage of the third inorganic insulating layer **109**. The surface of the third inorganic insulating layer **109** has the plurality of irregularities **110**, whereby the adhesion between the surface of the third inorganic insulating layer **109** and a film to be formed on the third inorganic insulating layer **109** can be increased.

In this embodiment, the adhesion between the second inorganic insulating layer **104** and the third inorganic insulating layer **109**, and between the surface of the third inorganic insulating layer **109** and the film to be formed on the third inorganic insulating layer **109** can be increased. Accordingly, the degree of peeling of a film at an edge portion can be reduced particularly in the preservation test under high temperature and high humidity conditions. That is, a semiconductor device with improved water resistance and reliability can be provided.

As has been described above, in the semiconductor device shown in this embodiment, the adhesion between the second inorganic insulating layer **104** and the third inorganic insulating layer **109**, and between the surface of the third inorganic insulating layer **109** and the film to be formed on the third inorganic insulating layer **109** can be increased; thus, the degree of peeling of a film at an edge portion can be reduced particularly in the preservation test under high temperature and high humidity conditions. Accordingly, intrusion of moisture into the semiconductor element layer from an interface between the second inorganic insulating layer and the third inorganic insulating layer can be suppressed. That is, heat resistance and moisture resistance can be improved, and a semiconductor device with improved reliability and a method for manufacturing the semiconductor device can be provided.

Note that in this embodiment, what is illustrated in the drawing can be freely combined with or replaced with what is described in other embodiments as appropriate.

Embodiment 2

In this embodiment, an example of a semiconductor device which is different from that shown in Embodiment 1 will be described with reference to FIGS. **5A** to **5C** and FIGS. **6A** and **6B**.

As described in Embodiment 1, first, the first inorganic insulating layer **102** is formed over the substrate **101**. Then, the semiconductor element layer **103** is formed over the first inorganic insulating layer **102**, and the opening portion **105** is formed between the semiconductor element layers **103**. Next, the second inorganic insulating layer **104** is formed so as to

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cover the semiconductor element layers **103**. Then, the organic insulating layer **106** is formed over the second inorganic insulating layer **104**, and etching is performed so that the organic insulating layer **106** remains over the semiconductor element layer **103** with the second inorganic insulating layer **104** interposed therebetween, whereby the opening portions **107** are formed (FIG. 5A).

Note that description of the substrate **101**, the first inorganic insulating layer **102**, the semiconductor element layer **103**, the opening portion **105**, the second inorganic insulating layer **104**, the organic insulating layer **106**, and the opening portion **107** is similar to the description of FIGS. 1A to 1C in Embodiment 1; therefore, detailed description is not repeated here.

Next, a plurality of opening portions **501** are formed in the second inorganic insulating layer **104** in a region where the first inorganic insulating layer **102** and the second inorganic insulating layer **104** are in direct contact with each other (FIG. 5B). The plurality of opening portions **501** may be formed through steps such as resist application using a photosensitive resin called a photoresist, pattern exposure, development, selective etching by anisotropic etching using the resist as a mask, and resist removal by using a lithography technique. Note that as illustrated in FIG. 5B, the cross-sectional shape of the surface of the plurality of opening portions **501** may be columnar. Alternatively, the cross-sectional shape of the plurality of opening portions **501** may be rounded as illustrated in FIG. 6A, or may be substantially pointed as illustrated in FIG. 6B.

Then, the third inorganic insulating layer **109** is formed to cover the organic insulating layer **106** and the second inorganic insulating layer **104** provided with the plurality of opening portions **501** (FIG. 5C). As in Embodiment 1, the third inorganic insulating layer **109** can prevent diffusion of moisture and impurities from the organic insulating layer **106**. Further, the plurality of opening portions **501** are formed in the second inorganic insulating layer **104**, whereby the area where the second inorganic insulating layer **104** and the third inorganic insulating layer **109** are in direct contact with each other can be increased. Accordingly, the adhesion between the second inorganic insulating layer **104** and the third inorganic insulating layer **109** can be increased.

In this embodiment, by forming the plurality of opening portions **501** in the second inorganic insulating layer **104**, a region where the first inorganic insulating layer **102** and the third inorganic insulating layer **109** are in direct contact with each other can be formed. Accordingly, the adhesion between the first insulating layer **102** and the third inorganic insulating layer **109** can be increased.

Note that description of the third inorganic insulating layer **109** is similar to the description of FIG. 1E in Embodiment 1; therefore, detailed description is not repeated here.

Moreover, in a region where the third inorganic insulating layer **109** overlaps with the plurality of opening portions **501** in the second inorganic insulating layer **104**, a surface of the third inorganic insulating layer **109** has the plurality of irregularities **110**. Note that as illustrated in FIG. 5C, the size or depth of the opening in a cross section of the plurality of irregularities **110** of the surface of the third inorganic insulating layer **109** varies depending on the size or depth of the opening in the plurality of opening portions **501** in the second inorganic insulating layer **104** or the thickness or step coverage of the third inorganic insulating layer **109**. The surface of the third inorganic insulating layer **109** has the plurality of irregularities **110**, whereby the adhesion between the surface

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of the third inorganic insulating layer **109** and the film to be formed on the third inorganic insulating layer **109** can be increased.

In this embodiment, the adhesion between the second inorganic insulating layer **104** and the third inorganic insulating layer **109**, between the first inorganic insulating layer **102** and the third inorganic insulating layer **109**, and between the surface of the third inorganic insulating layer **109** and the film to be formed on the third inorganic insulating layer **109** can be increased. Accordingly, the degree of peeling of a film at an edge portion can be reduced particularly in the preservation test under high temperature and high humidity conditions. That is, a semiconductor device with improved water resistance and reliability can be provided.

As has been described above, in the semiconductor device shown in this embodiment, the adhesion between the second inorganic insulating layer **104** and the third inorganic insulating layer **109**, between the first inorganic insulating layer **102** and the third inorganic insulating layer **109**, and between the surface of the third inorganic insulating layer **109** and the film to be formed on the third inorganic insulating layer **109** can be increased. Thus, the degree of peeling of a film at an edge portion can be reduced particularly in the preservation test under high temperature and high humidity conditions. Accordingly, moisture can be prevented from entering the semiconductor element layer from interfaces between the first inorganic insulating layer **102** and the third inorganic insulating layer **109**, between the second inorganic insulating layer **104** and the third inorganic insulating layer **109**, and between the surface of the third inorganic insulating layer **109** and the film to be formed on the third inorganic insulating layer **109**. That is, a semiconductor device with improved water resistance and reliability and a method for manufacturing the semiconductor device can be provided.

Note that in this embodiment, what is illustrated in the drawing can be freely combined with or replaced with what is described in other embodiments as appropriate.

Embodiment 3

In this embodiment, the semiconductor device described in Embodiment 2 and a method for manufacturing the semiconductor device will be specifically described.

This embodiment will be described with reference to FIGS. 7A to 7F and FIGS. 15A to 15F. Note that FIGS. 15A to 15F are top views corresponding to the cross-sectional views of FIGS. 7A to 7F.

First, a first inorganic insulating layer **702** is formed over a substrate **701** (see FIG. 7A and FIG. 15A).

Note that description of the substrate **701** and the first inorganic insulating layer **702** is similar to the description of the substrate **101** and the first inorganic insulating layer **102** illustrated with reference to FIG. 1A in Embodiment 1; therefore, detailed description is not repeated here.

Next, a thin film transistor **703** is formed over the first inorganic insulating layer **702**. Note that the thin film transistor **703** is not necessarily formed on the first inorganic insulating layer **702**. Alternatively, a base film (not shown) may be formed and a thin film transistor may be formed over the base film.

The thin film transistor **703** formed over the first inorganic insulating layer **702** includes a semiconductor layer **704** having a source region, a drain region, and a channel formation region; a gate insulating layer **705**; and a gate electrode **706**. Then, an interlayer insulating film **707** is formed to cover the thin film transistor **703**. Moreover, wirings **708** that are in contact with the source region and the drain region in the

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semiconductor layer **704** are formed over the interlayer insulating film **707**. After the wirings **708** are formed, etching is performed so that the gate insulating layer **705** and the interlayer insulating film **707** are divided into semiconductor devices, whereby opening portions **709** are formed between the thin film transistors **703** (see FIG. 7B and FIG. 15B).

Note that description of the gate insulating layer **705**, the gate electrode **706**, the interlayer insulating film **707**, and the wiring **708** is similar to the description of the gate insulating layer **205**, the gate electrode **206**, the interlayer insulating films **207** to **209**, and the wiring **210** illustrated with reference to FIG. 2 in Embodiment 1; therefore, detailed description is not repeated here.

Note that as in the description of FIG. 2 in Embodiment 1, the semiconductor device shown in this embodiment does not necessarily have a structure including a thin film transistor and may include a plurality of elements formed using semiconductor characteristics. For example, the semiconductor device may include a diode, a resistor, a capacitor, a memory element, or the like in addition to a thin film transistor.

Next, a second inorganic insulating layer **711** is formed so as to cover the interlayer insulating film **707**, the wiring **708**, and the opening portions **709**. Then, an organic insulating layer **712** is formed over the second inorganic insulating layer **711**, and etching is performed so that the organic insulating layer **712** remains over the thin film transistor **703** with the second inorganic insulating layer **711** interposed therebetween, whereby opening portions **713** are formed. Moreover, an opening **714** for realizing electrical connection with the wiring **708** of the thin film transistor **703** in a later step is formed in the organic insulating layer **712** (see FIG. 7C and FIG. 15C). In this embodiment, the thin film transistor **703** can be surrounded by the first inorganic insulating layer **702** and the second inorganic insulating layer **711** as in Embodiment 1, whereby intrusion of impurities and moisture into the semiconductor layer **704** can further be suppressed, and a semiconductor device with higher reliability can be obtained.

Note that description of the second inorganic insulating layer **711** and the organic insulating layer **712** is similar to the description of the second inorganic insulating layer **104** and the organic insulating layer **106** illustrated in FIG. 5A in Embodiment 2; therefore, detailed description is not repeated here.

Next, etching treatment for forming an opening **715** that reaches the wiring **708** is performed on the opening **714** for realizing electrical connection with the wiring **708** of the thin film transistor **703** in a later step, and at the same time, a plurality of opening portions **716** are formed in the second inorganic insulating layer **711** in the opening portion **713** where the first inorganic insulating layer **702** and the second inorganic insulating layer **711** are in direct contact with each other (see FIG. 7D and FIG. 15D). The plurality of opening portions **716** may be formed through steps such as resist application using a photosensitive resin called a photoresist, pattern exposure, development, selective etching by anisotropic etching using the resist as a mask, and resist removal by using a lithography technique. Note that as has been described with reference to FIGS. 6A and 6B in Embodiment 2, there is no particular limitation on the shape of the surface of the plurality of opening portions **716**.

In the structure in this embodiment, the plurality of opening portions **716** can be formed in the second inorganic insulating layer **711** at the same time as the etching treatment for forming the opening **715** that reaches the wiring **708**. Accordingly, it is not necessary to use an additional photomask for providing a plurality of opening portions in the second inor-

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ganic insulating layer by lithography. Thus, the number of photomasks for forming a semiconductor device can be reduced.

Then, a conductive layer **717** that is electrically connected to the wiring **708** is formed over the openings **714** and **715** and the organic insulating layer **712** (see FIG. 7E and FIG. 15E). In this embodiment, the conductive layer **717** is formed using a stack of a titanium film and an aluminum film. For example, the conductive layer **717** functions as an antenna for receiving a wireless signal from the outside.

Next, a third inorganic insulating layer **718** is formed to cover the second inorganic insulating layer **711**, the organic insulating layer **712**, and the conductive layer **717**. Then, as has been described in Embodiment 2, in a region where the inorganic insulating layer **718** overlaps with the plurality of opening portions **716** provided in the second inorganic insulating layer **711**, a surface of the third inorganic insulating layer **718** is formed to have a plurality of irregularities **719** (see FIG. 7F and FIG. 15F). The surface of the third inorganic insulating layer **718** has the plurality of irregularities **719**, whereby the adhesion between the surface of the third inorganic insulating layer **718** and a film to be formed on the third inorganic insulating layer **718** can be increased particularly in the preservation test under high temperature and high humidity conditions.

As in Embodiment 1, the third inorganic insulating layer **718** functions as a blocking film for preventing impurities and moisture from entering the conductive layer **717** and the thin film transistor **703** surrounded by the first inorganic insulating layer **702** and the second inorganic insulating layer **711**.

As has been described above, in the semiconductor device shown in this embodiment, the adhesion between the second inorganic insulating layer **711** and the third inorganic insulating layer **718**, between the first inorganic insulating layer **702** and the third inorganic insulating layer **718**, and between the surface of the third inorganic insulating layer **718** and the film to be formed on the third inorganic insulating layer **718** can be increased. Thus, the degree of peeling of a film at an edge portion can be reduced particularly in the preservation test under high temperature and high humidity conditions. Accordingly, moisture can be prevented from entering the thin film transistor **703** from interfaces between the first inorganic insulating layer **702** and the third inorganic insulating layer **718**, between the second inorganic insulating layer **711** and the third inorganic insulating layer **718**, and between the surface of the third inorganic insulating layer **718** and the film to be formed on the third inorganic insulating layer **718**. That is, heat resistance and moisture resistance can be improved, and a semiconductor device with improved reliability and a method for manufacturing the semiconductor device can be provided.

In addition, in the structure in this embodiment, the plurality of opening portions **716** can be formed in the second inorganic insulating layer **711** at the same time as the etching treatment for forming the opening **715** that reaches the wiring **708**. Accordingly, it is not necessary to use an additional photomask for providing a plurality of opening portions in the second inorganic insulating layer by lithography, whereby a method for manufacturing the semiconductor device in which the number of photomasks can be reduced can be provided.

Note that in this embodiment, what is illustrated in the drawing can be freely combined with or replaced with what is described in other embodiments as appropriate.

Embodiment 4

In this embodiment, a method for manufacturing the semiconductor device, which is different from that described in Embodiment 3, will be described.

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This embodiment will be described with reference to FIGS. 8A to 8D, FIGS. 9A to 9C, FIG. 10, and FIGS. 11A and 11B.

A cross-sectional structure of a semiconductor device illustrated in FIG. 8A is such that a separation layer 801 is additionally provided between the substrate 701 and the first inorganic insulating layer 702 in the cross-sectional structure illustrated in FIG. 7F of Embodiment 3. FIG. 8A illustrates the substrate 701, the first inorganic insulating layer 702, the semiconductor layer 704, the gate insulating layer 705, the gate electrode 706, the interlayer insulating film 707, the wiring 708, the second inorganic insulating layer 711, the organic insulating layer 712, the plurality of opening portions 716, the conductive layer 717, the third inorganic insulating layer 718, and the plurality of irregularities 719. Note that steps for stacking layers from the first inorganic insulating layer 702 to the third inorganic insulating layer 718 are similar to those in Embodiment 3; therefore, the description is not repeated in this embodiment.

The separation layer 801 is formed using a single layer or a stack of a layer that has a thickness of 30 nm to 200 nm and is formed using an element selected from tungsten (W), molybdenum (Mo), titanium (Ti), tantalum (Ta), niobium (Nb), nickel (Ni), cobalt (Co), zirconium (Zr), zinc (Zn), ruthenium (Ru), rhodium (Rh), palladium (Pd), osmium (Os), iridium (Ir), or silicon (Si); or an alloy material or a compound material containing any of the above elements as its main component by a sputtering method, a plasma CVD method, a coating method, a printing method, or the like. A structure of a layer containing silicon may be amorphous, microcrystalline, or polycrystalline. Note that a coating method refers to a method in which a solution is discharged on an object to form a film, and includes, for example, a spin coating method and a droplet discharging method in its category. A droplet discharging method refers to a method in which droplets of a composition containing fine particles are discharged from a small hole to form a predetermined pattern.

When the separation layer 801 has a single-layer structure, it is preferable to form a layer containing tungsten, molybdenum, or a mixture of tungsten and molybdenum. Alternatively, a layer containing oxide or oxynitride of tungsten, a layer containing oxide or oxynitride of molybdenum, or a layer containing oxide or oxynitride of a mixture of tungsten and molybdenum may be formed. Note that a mixture of tungsten and molybdenum corresponds to an alloy of tungsten and molybdenum, for example.

When the separation layer 801 has a stacked structure, it is preferable that a metal layer be formed as a first layer and a metal oxide layer be formed as a second layer. Typically, a layer containing tungsten, molybdenum, or a mixture of tungsten and molybdenum is formed as the metal layer of the first layer. As the second layer, a layer containing oxide of tungsten, molybdenum, or a mixture of tungsten and molybdenum; nitride of tungsten, molybdenum, or a mixture of tungsten and molybdenum; oxynitride of tungsten, molybdenum, or a mixture of tungsten and molybdenum; or nitride oxide of tungsten, molybdenum, or a mixture of tungsten and molybdenum is formed.

Next, after the state of FIG. 8A is obtained, a first sealing layer 802 including a fibrous body and an organic resin layer is formed over the third inorganic insulating layer 718 and the plurality of irregularities 719 and bonded by pressing (see FIG. 8B).

The first sealing layer 802 includes the fibrous body and the organic resin layer. The fibrous body is a woven fabric or a nonwoven fabric which uses a high-strength fiber of an organic compound or an inorganic compound. The high-strength fiber is specifically a fiber with a high tensile modulus

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of elasticity or a fiber with a high Young's modulus. Typical examples of the high-strength fiber are a polyvinyl alcohol fiber, a polyester fiber, a polyamide fiber, a polyethylene fiber, an aramid fiber, a polyparaphenylene benzobisoxazole fiber, a glass fiber, and a carbon fiber. As the glass fiber, a glass fiber using E glass, S glass, D glass, Q glass, or the like can be used. Note that the fibrous body may be formed from one kind or a plurality of the above high-strength fibers.

When a carbon fiber is used as the fibrous body so that the fibrous body is electrically conductive, electrostatic discharge can be reduced.

The fibrous body may be formed using a woven fabric which is woven using bundles of fibers (single yarn) (hereinafter referred to as yarn bundles) for warp yarns and weft yarns, or a nonwoven fabric obtained by stacking yarn bundles of plural kinds of fibers in a random manner or in one direction.

The yarn bundle may have a circular shape or an elliptical shape in cross section. As the bundle of fibers, a bundle of fibers which has been subjected to fiber opening with a high-pressure water stream, high-frequency vibration using liquid as a medium, continuous ultrasonic vibration, pressing with a roller, or the like may be used. A bundle of fibers which is subjected to fiber opening has a large width, has a smaller number of single yarns in the thickness direction, and has a cross section of an elliptical shape or a flat shape. Further, when a loosely twisted yarn is used as the bundle of fibers, the fiber bundle is easily flattened and has a cross section of an elliptical shape or a flat shape. By using a fiber bundle having a cross section of an elliptical shape or a flat shape as described above, it is possible to make the fibrous body thinner. Accordingly, the sealing layer can be made thinner, and thus, a thin semiconductor device can be manufactured. Although the diameter of the fiber bundle is preferably equal to or greater than 4 μm and equal to or less than 400 μm , more preferably equal to or greater than 4 μm and equal to or less than 200 μm , it is theoretically possible that the diameter of the fiber bundle is even smaller. Moreover, although the thickness of the fiber is preferably equal to or greater than 4 μm and equal to or less than 20 μm , it is theoretically possible that the thickness of the fiber is even smaller, and the thickness of the fiber depends on a material of the fiber.

The thickness of the first sealing layer 802 is preferably equal to or greater than 10 μm and equal to or less than 100 μm , more preferably equal to or greater than 10 μm and equal to or less than 30 μm . When the sealing layer with such a thickness is used, a thin semiconductor device capable of being bent can be formed.

As an example of a press step for bonding the first sealing layer 802 including the fibrous body and the organic resin layer to the third inorganic insulating layer 718 and the plurality of irregularities 719, the temperature is raised from a room temperature to 100° C. in 30 minutes in a vacuum atmosphere, and then, the temperature is kept at 135° C. under a pressure of 0.3 MPa for 15 minutes so that the first sealing layer 802 is uniformly fixed to the third inorganic insulating layer 718, and after that, the temperature is raised to 195° C. and kept for 60 minutes.

Next, an adhesive tape 803 which can be separated by light or heat is provided over the first sealing layer 802. Then, separation is performed at the separation layer 801 while a roller 804 rotates on the adhesive tape 803 (see FIG. 8C), so that the substrate 701 and the separation layer 801 are physically separated (see FIG. 8D).

Next, a second sealing layer 805 including a fibrous body and an organic resin layer is formed in contact with a surface of the first inorganic insulating layer 702, which is exposed by

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separating the separation layer **801**, and is bonded by pressing (see FIG. **9A**). Note that the adhesive tape **803** may be separated before or after the second sealing layer **805** is provided.

Note that description of the second sealing layer **805** is similar to that of the first sealing layer **802**; therefore, detailed description is not repeated.

Then, laser beams (shown by arrows) are emitted to regions between elements, that is, regions provided with the plurality of opening portions **716** formed in the second inorganic insulating layer between semiconductor element layers, and chips are cut out (see FIG. **9B**). Thus, a plurality of semiconductor devices **806** can be obtained (see FIG. **9C**).

The above is one example of manufacturing the semiconductor device.

Note that the semiconductor device shown in this embodiment functions as a semiconductor device that can transmit and receive data without contact. For example, the conductive layer **717** in this embodiment functions as an antenna. Moreover, a layer including a thin film transistor having the semiconductor layer **704**, the gate insulating layer **705**, and the gate electrode **706**, functions as a semiconductor element layer included in a logic circuit or the like. FIG. **10** is a top view in the case where a semiconductor device is formed by separating the layers including a plurality of semiconductor devices from a substrate and cutting the layers into respective semiconductor devices. Note that the top view of FIG. **10** corresponds to the cross-sectional view of FIG. **9B**.

The top view of FIG. **10** illustrates, inside a sealing layer **1001**, a semiconductor element layer **1002**, an antenna **1003**, and a region **1004** where a plurality of opening portions are formed. The region **1004** where the plurality of opening portions are formed is irradiated with laser beams, so that regions where the semiconductor element layer **1002** and the antenna **1003** are formed can be separated. As has been described in the above embodiments, the region **1004** where the plurality of opening portions are formed can improve the adhesion between the second inorganic insulating layer **711** and the third inorganic insulating layer **718**, between the first inorganic insulating layer **702** and the third inorganic insulating layer **718**, and between the surface of the third inorganic insulating layer **718** and the first sealing layer **802**. Thus, the degree of peeling of a film at an edge portion can be reduced particularly in the preservation test under high temperature and high humidity conditions. Accordingly, moisture can be prevented from entering the semiconductor element layer **1002** and the antenna **1003** from interfaces between the first inorganic insulating layer **702** and the third inorganic insulating layer **718**, between the second inorganic insulating layer **711** and the third inorganic insulating layer **718**, and between the surface of the third inorganic insulating layer **718** and the first sealing layer **802**. That is, a semiconductor device with improved water resistance and reliability and a method for manufacturing the semiconductor device can be provided.

Note that the cross-sectional view of FIG. **9C** illustrates the structure in which one transistor is included as a transistor interposed between the first sealing layer **802** and the second sealing layer **805**; however, the structure of the semiconductor device is not particularly limited thereto. For example, when a plurality of elements such as a p-channel transistor, an n-channel transistor, a diode, a resistor, a capacitor, and a memory element are included, the semiconductor device includes several tens of thousands of elements. As an example, FIG. **16** illustrates a structure where a p-channel transistor including a semiconductor layer **704A** and an n-channel transistor including a semiconductor layer **704B** are interposed between the first sealing layer **802** and the second sealing layer **805**. In the semiconductor layer **704A**,

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an element imparting p-type conductivity is added to a source region and a drain region. In the semiconductor layer **704B**, an element imparting n-type conductivity is added to a source region and a drain region. Note that FIG. **16** illustrates one p-channel transistor and one n-channel transistor. In an actual semiconductor device, a plurality of p-channel transistors and n-channel transistors are placed in the lateral direction and the depth direction.

FIGS. **11A** and **11B** show photographs for describing effect of a plurality of opening portions in a semiconductor device. Note that FIGS. **11A** and **11B** are photographs of samples in which the structure described in this embodiment is experimentally reproduced. FIG. **11A** shows a photograph of samples without a plurality of opening portions after the preservation test under high temperature and high humidity conditions. FIG. **11B** shows a photograph of samples with a plurality of opening portions after the preservation test under high temperature and high humidity conditions. Note that since it is extremely difficult to draw the samples in FIGS. **11A** and **11B** by graphics, the samples are shown by the photographs instead of being drawn by the graphics.

Note that in this specification, the preservation test under high temperature and high humidity conditions refers to a test in which change after 500 hours at a temperature of 85° C. and a humidity of 85% is observed by visual inspection and an optical microscope.

It can be found from the photographs in FIGS. **11A** and **11B** that, in the semiconductor device with a plurality of opening portions, the degree of peeling of a film after the preservation test under high temperature and high humidity conditions can be reduced as compared to that in the semiconductor device without a plurality of opening portions (in FIG. **11A**). That is, a semiconductor device with improved water resistance and reliability and a method for manufacturing the semiconductor device can be provided.

FIGS. **11A** and **11B** show that the provision of a plurality of opening portions is effective in reducing the degree of peeling of a film after the preservation test under high temperature and high humidity conditions. Moreover, it was found that the structure in which a silicon nitride film and a silicon oxynitride film was stacked for the first inorganic insulating layer **102** was effective in further reducing the degree of peeling of a film after the preservation test under high temperature and high humidity conditions. Further, it was also found by an optical microscope that peeling of a film after the preservation test under high temperature and high humidity conditions could be prevented by the structure in which a silicon nitride film and a silicon oxynitride film was stacked for the first inorganic insulating layer **102** and a transistor was interposed between sealing layers including a fibrous body and an organic resin layer.

Note that in this embodiment, what is illustrated in the drawing can be freely combined with or replaced with what is described in other embodiments as appropriate.

Embodiment 5

This embodiment will show application examples of a semiconductor device. Here, an RFID tag (also referred to as an IC tag) will be described as an application example of the semiconductor device.

First, a circuit configuration example of an RFID tag to which the semiconductor device is applied will be described. FIG. **12** is a block circuit diagram of the RFID tag.

The RFID tag in FIG. **12** conforms to specifications of ISO 15693 of the International Organization for Standardization, is a vicinity type, and has a communication signal frequency

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of 13.56 MHz. Moreover, reception only responds to a data reading instruction, the data transmission rate in transmission is approximately 13 kHz, and the Manchester code is used for data coding.

A circuit portion **1212** of the RFID tag is roughly divided into a power supply portion **1260** and a signal processing portion **1261**. The power supply portion **1260** includes a rectifier circuit **1262** and a storage capacitor **1263**. Further, the power supply portion **1260** may be provided with a protection circuit portion (also referred to as a limiter circuit portion) for protecting the internal circuit when an excessive amount of electric power is received by an antenna **1211**, and a protection circuit control circuit portion for controlling whether or not to operate the protection circuit portion. The provision of the circuit portions can prevent malfunction caused when the RFID tag receives a large amount of electric power under the situation in which a communication range between the RFD tag and a communication device is extremely short, for example. Accordingly, the reliability of the RFID tag can be improved. That is, the RFID tag can be normally operated without degradation of an element in the RFID tag or destruction of the RFID tag itself.

The circuit portion **1212** is formed in the semiconductor element layer **103**, described in Embodiments 1 and 2.

Note that in this embodiment, a communication device has a means to transmit and receive information to/from the RFD tag by wireless communication. Examples of the communication device are a reader that reads information; a reader/writer that has a reading function and a writing function; and a mobile phone, a computer, and the like which have one or both of the read function and the write function.

The rectifier circuit **1262** rectifies a carrier wave received by the antenna **1211** and generates direct-current voltage. The storage capacitor **1263** smoothes the direct-current voltage generated in the rectifier circuit **1262**. The direct-current voltage generated in the power supply portion **1260** is supplied to each circuit in the signal processing portion **1261** as power supply voltage.

The signal processing portion **1261** includes a demodulation circuit **1264**, a clock generation/correction circuit **1265**, a recognition/determination circuit **1266**, a memory controller **1267**, a mask ROM **1268**, an encoding circuit **1269**, and a modulation circuit **1270**.

The demodulation circuit **1264** demodulates a signal received by the antenna **1211**. The received signal which is demodulated by the demodulation circuit **1264** is input to the clock generation/correction circuit **1265** and the recognition/determination circuit **1266**.

The clock generation/correction circuit **1265** has functions of generating a clock signal which is necessary for operating the signal processing portion **1261**, and correcting the clock signal. For example, the clock generation/correction circuit **1265** includes a voltage controlled oscillator circuit (hereinafter referred to as a VCO circuit), employs an output of the VCO circuit as a feedback signal, compares phases between a supplied signal and the feedback signal, and adjusts an output signal by using negative feedback so that the signal to be input and the feedback signal have a certain phase.

The recognition/determination circuit **1266** recognizes and determines an instruction code. The instruction code recognized and determined by the recognition/determination circuit **1266** is an end-of-frame (EOF) signal, a start-of-frame (SOF) signal, a flag, a command code, a mask length, a mask value, or the like. Moreover, the recognition/determination circuit **1266** has a cyclic redundancy check (CRC) function that identifies a transmission error.

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The memory controller **1267** reads data from the mask ROM **1268** in response to a signal processed by the recognition/determination circuit **1266**. An ID or the like is stored in the mask ROM **1268**. The mask ROM **1268** is mounted on the RFID tag, whereby the read-only RFID tag in which data is incapable of being replicated or altered is formed. When such a read-only RFID tag is embedded in paper, forgery prevention paper can be obtained.

The encoding circuit **1269** encodes the data which is read from the mask ROM **1268** by the memory controller **1267**. The encoded data is modulated by the modulation circuit **1270**. The data modulated by the modulation circuit **1270** is transmitted from the antenna **1211** as a carrier wave.

Next, usage examples of the RFID tag will be described. The RFID tag can be used for a variety of paper media and film media. In particular, the RFID tag having the structure described in the above embodiments can be used for a variety of paper media for which forgery prevention is necessary. Examples of the paper media are banknotes, family registers, residence certificates, passports, licenses, identification cards, membership cards, expert opinions in writing, patient's registration cards, commuter passes, promissory notes, checks, carriage notes, cargo certificates, warehouse certificates, stock certificates, bond certificates, gift certificates, tickets, and deeds of mortgage.

Further, by the RFID tag having the structure described in the above embodiments, a lot more information than that which is visually shown on a paper medium can be held in the paper medium or the film medium. Accordingly, when the RFID tag is applied to a product label or the like, development of an electronic system for merchandise management or prevention of product theft can be realized. Usage examples of the paper are described below with reference to FIGS. **13A** to **13E**.

FIG. **13A** illustrates an example of a bearer bond **1311** using paper embedded with an RFID tag **1301**. The bearer bond **1311** includes, but is not limited to, a stamp, a ticket, an admission ticket, a gift certificate, a book coupon, a stationery coupon, a beer coupon, a rice coupon, a variety of gift coupons, and a variety of service coupons in its category. Further, FIG. **13B** illustrates an example of a certificate **1312** (e.g., a residence certificate or a family register) using the paper embedded with the RFID tag **1301**.

FIG. **13C** illustrates an example in which the RFID tag having the structure described in the above embodiments is applied to a label. Over a label base (separate paper) **1313**, a label (an ID sticker) **1314** is formed using the paper embedded with the RFID tag **1301**. The label **1314** is stored in a box **1315**. On the label **1314**, information regarding a product or a service (such as product name, brand, trademark, trademark owner, seller, or manufacturer) is printed. Moreover, a unique ID number of the product (or a category of the product) is stored in the RFID tag **1301**, whereby forgery, infringement of intellectual property rights such as a trademark right or a patent right, and illegal activity such as unfair competition can be easily spotted. The RFID tag **1301** can be input with a large amount of information that cannot all be written on a container or a label of the product, such as home of the production, area of sales, quality, raw material, effect, use, quantity, shape, price, production method, usage method, time of production, time of use, expiration date, instruction manual, and intellectual property information relating to the product, for example. Accordingly, a transactor or a consumer can access such information with a simple communication device. Further, the information can be easily rewritten and erased, for example, by a producer, but cannot be rewritten and erased, for example, by the transactor or the consumer.

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FIG. 13D illustrates a tag 1316 formed using paper or a film which is embedded with the RFID tag 1301. By forming the tag 1316 by using the paper or the film which is embedded with the RFID tag 1301, the tag can be manufactured at lower cost than a conventional ID tag using a plastic housing. FIG. 13E illustrates a book 1317 in which the RFID tag is used for the cover. The RFID tag 1301 is embedded in the cover.

The label 1314 or the tag 1316 provided with the RFID tag, which is an example of the semiconductor device, is attached to the product, whereby merchandise management becomes easy. For example, when the product is stolen, the perpetrator can be spotted quickly by following a route of the product. In such a manner, by using the RFID tag as an ID tag, tracking inquiry and historical management of the product's raw material, area of production, manufacturing and processing, distribution, sales, and the like are possible. That is, the product can be traceable.

Note that in this embodiment, what is illustrated in the drawing can be freely combined with or replaced with what is described in other embodiments as appropriate. That is, the present invention can provide a semiconductor device with improved water resistance and reliability and a method for manufacturing the semiconductor device.

This application is based on Japanese Patent Application serial No. 2008-109119 filed with Japan Patent Office on Apr. 18, 2008, the entire contents of which are hereby incorporated by reference.

What is claimed is:

1. A semiconductor device comprising:
a first inorganic insulating layer, a semiconductor element layer, a second inorganic insulating layer, an organic insulating layer, and a third inorganic insulating layer that are sequentially stacked over a substrate,
wherein the second inorganic insulating layer is in contact with the first inorganic insulating layer in a first opening portion provided in the semiconductor element layer,
wherein the third inorganic insulating layer is in contact with the second inorganic insulating layer in a second opening portion provided in the organic insulating layer, and
wherein in a region where the second inorganic insulating layer and the third inorganic insulating layer are in contact with each other, a surface of the second inorganic insulating layer has a plurality of irregularities.
2. The semiconductor device according to claim 1, wherein each of the first inorganic insulating layer, the second inorganic insulating layer, and the third inorganic insulating layer contains one of silicon nitride and silicon nitride oxide.
3. The semiconductor device according to claim 1, wherein the semiconductor element layer includes a thin film transistor.
4. The semiconductor device according to claim 1, wherein in a region where the third inorganic insulating layer overlaps with the plurality of irregularities of the second inorganic insulating layer, a surface of the third inorganic insulating layer has a plurality of irregularities.
5. The semiconductor device according to claim 1, wherein the semiconductor device further comprises a conductive layer electrically connected to the semiconductor element layer in a third opening portion provided in the organic insulating layer and the second inorganic insulating layer.
6. The semiconductor device according to claim 1, wherein the substrate is a flexible substrate.
7. A semiconductor device comprising:
a first inorganic insulating layer, a semiconductor element layer, a second inorganic insulating layer, an organic

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insulating layer, and a third inorganic insulating layer that are sequentially stacked over a substrate,
wherein the second inorganic insulating layer is in contact with the first inorganic insulating layer in a first opening portion provided in the semiconductor element layer,
wherein the third inorganic insulating layer is in contact with the second inorganic insulating layer in a second opening portion provided in the organic insulating layer, wherein in a region where the second inorganic insulating layer and the third inorganic insulating layer are in contact with each other, a plurality of opening portions are formed in the second inorganic insulating layer, and
wherein the first inorganic insulating layer and the third inorganic insulating layer are in contact with each other in the plurality of opening portions.

8. The semiconductor device according to claim 7, wherein each of the first inorganic insulating layer, the second inorganic insulating layer, and the third inorganic insulating layer contains one of silicon nitride and silicon nitride oxide.

9. The semiconductor device according to claim 7, wherein the semiconductor element layer includes a thin film transistor.

10. The semiconductor device according to claim 7, wherein in a region where the third inorganic insulating layer overlaps with the plurality of opening portions, a surface of the third inorganic insulating layer has a plurality of irregularities.

11. The semiconductor device according to claim 7, wherein the semiconductor device further comprises a conductive layer electrically connected to the semiconductor element layer in a third opening portion provided in the organic insulating layer and the second inorganic insulating layer.

12. The semiconductor device according to claim 7, wherein the substrate is a flexible substrate.

13. A semiconductor device comprising:
a first inorganic insulating layer, a thin film transistor, a second inorganic insulating layer, an organic insulating layer, and a third inorganic insulating layer that are sequentially stacked over a substrate,
wherein the second inorganic insulating layer is in contact with the first inorganic insulating layer with the thin film transistor interposed therebetween,
wherein the third inorganic insulating layer is in contact with the second inorganic insulating layer with the organic insulating layer interposed therebetween, and
wherein in a region where the second inorganic insulating layer and the third inorganic insulating layer are in contact with each other, a surface of the second inorganic insulating layer has a plurality of irregularities.

14. The semiconductor device according to claim 13, wherein each of the first inorganic insulating layer, the second inorganic insulating layer, and the third inorganic insulating layer contains one of silicon nitride and silicon nitride oxide.

15. The semiconductor device according to claim 13, wherein in a region where the third inorganic insulating layer overlaps with the plurality of irregularities of the second inorganic insulating layer, a surface of the third inorganic insulating layer has a plurality of irregularities.

16. The semiconductor device according to claim 13, wherein the semiconductor device further comprises a conductive layer electrically connected to the thin film transistor in an opening portion provided in the organic insulating layer and the second inorganic insulating layer.

17. The semiconductor device according to claim 13, wherein the substrate is a flexible substrate.

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